

Multipass Techniques

How to improve stitching, LER, LWR
and resolution

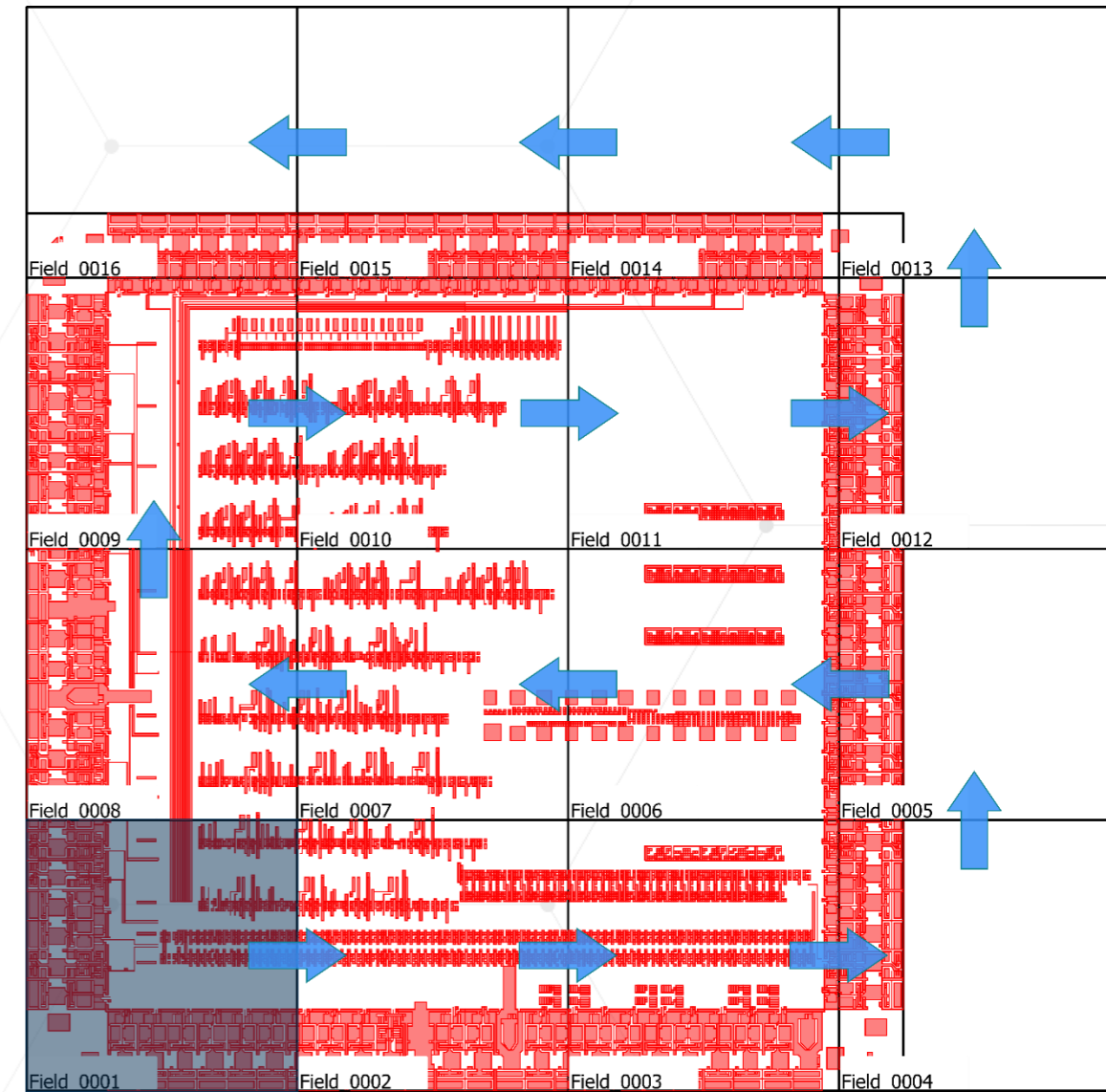
- Multipass with and without field shift
- Advanced Multipass Methods
 - How to retrieve throughput in traditional Multipass?
 - Interstitial field blend
 - Dose overlap
- Summary

Maximum field size is limited:

- E/O Field of View
- DAC-Bits binds field size to resolution

Large layouts need to be „tiled“:

- Uniform tile size
- Start bottom or top left
- Serpentine filling (Meander X)

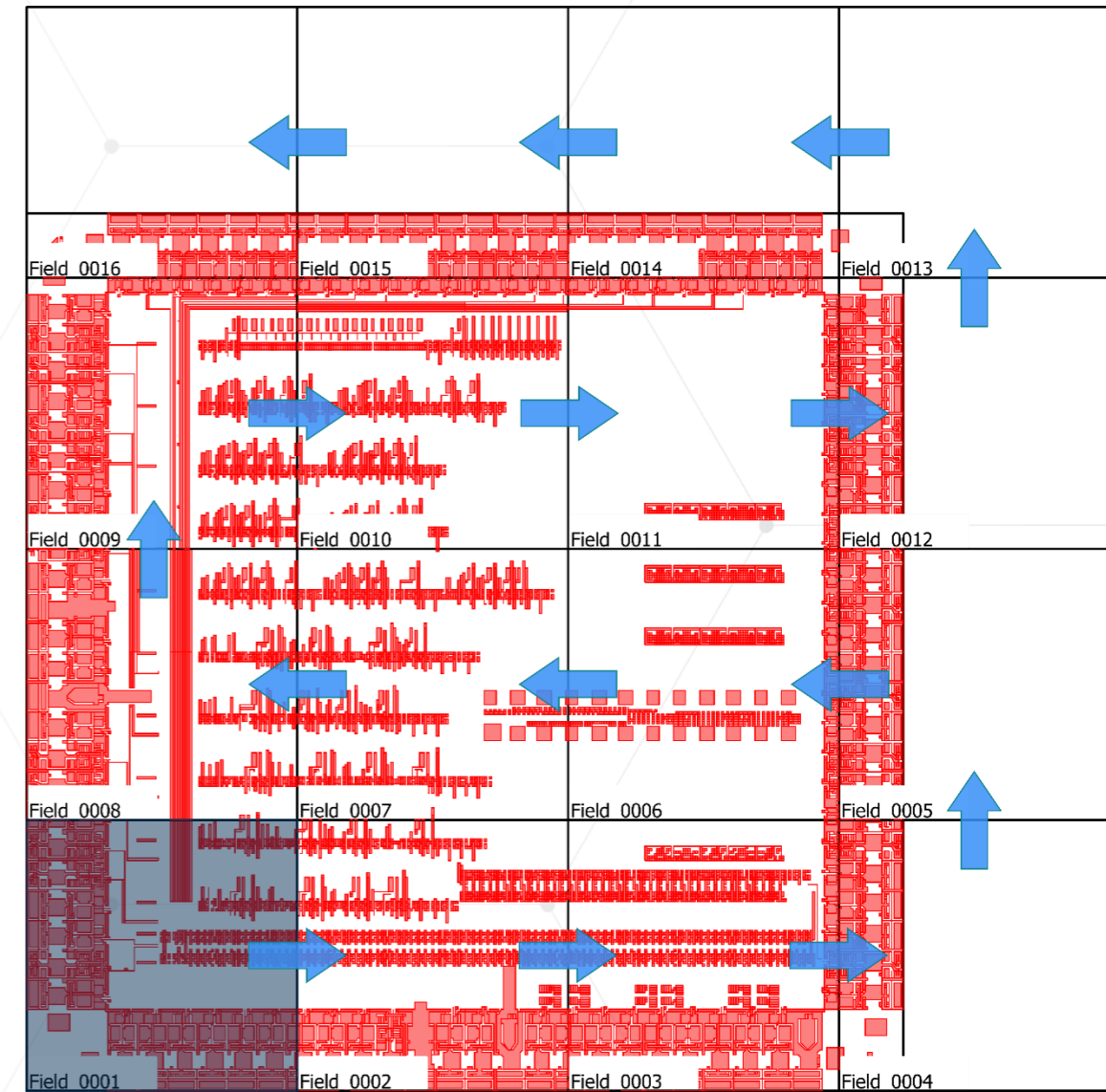


Issues within main field:

- Aberration depends on beam position within the field
- Thermal drift
- Mechanical vibration
- Sub-filed stitching

Issues field to field:

- Stitching at field borders



➔ Multipass method

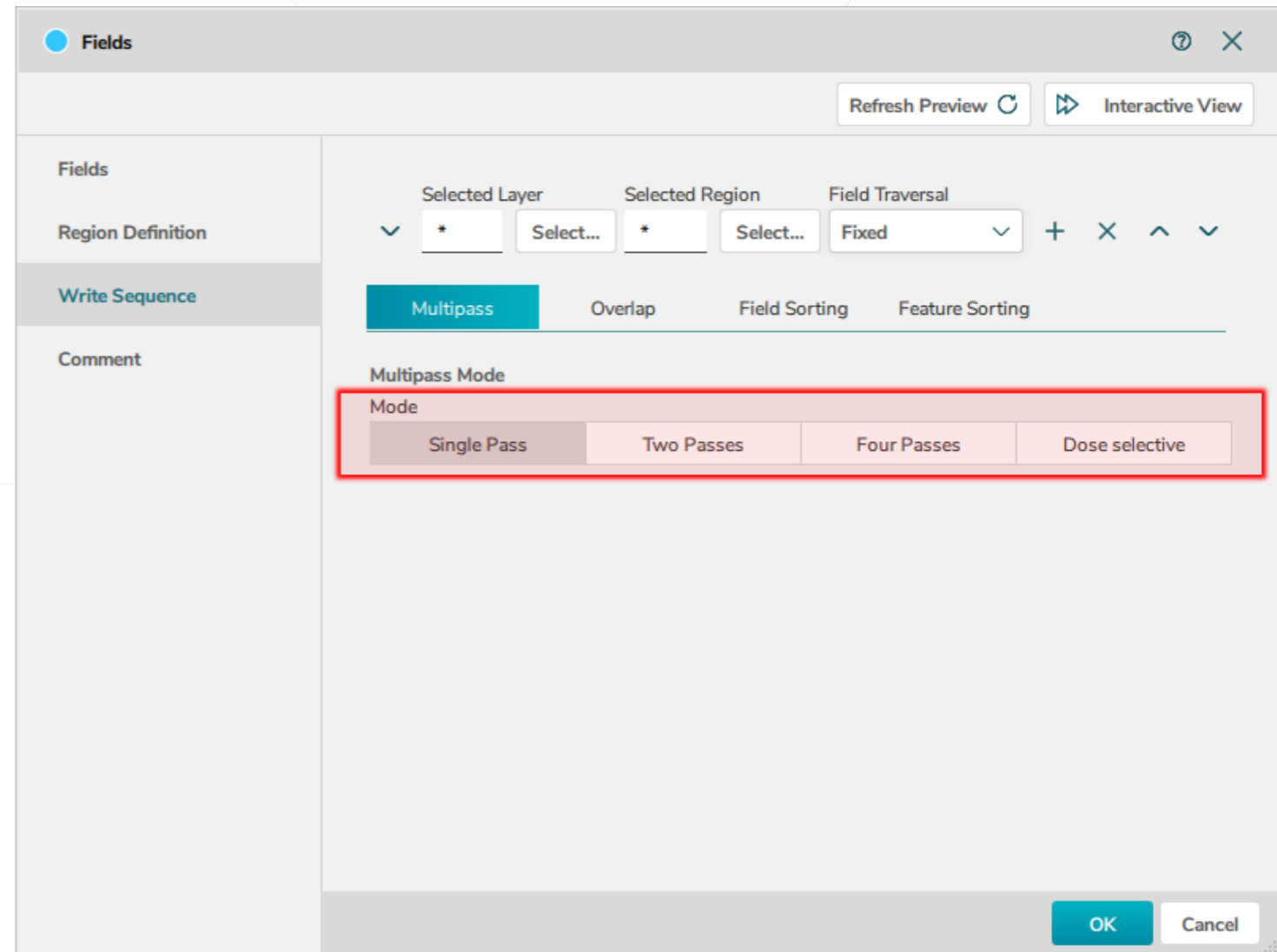
- Features are exposed multiple times at different locations in the field (centre of field, border of field)
- Fields are exposed in a successive and overlapping fashion

Why does Multipass work?

- **Multipass reduces statistical errors by averaging**
 - Beam Current Fluctuations
 - Beam Jitter, Beam Drift
 - Stage Position Errors, mechanical vibrations
- **Multipass reduces systematic errors by offsetting**
 - Field Distortion and Field Aberration
 - Scan Non-Linearities
 - Shutter Effect
 - X/Y asymmetries due to discrete spots in Y / dragging in X

- BEAMER supports:
 - Single pass
 - Two passes*
 - Four passes*
 - Dose selective*

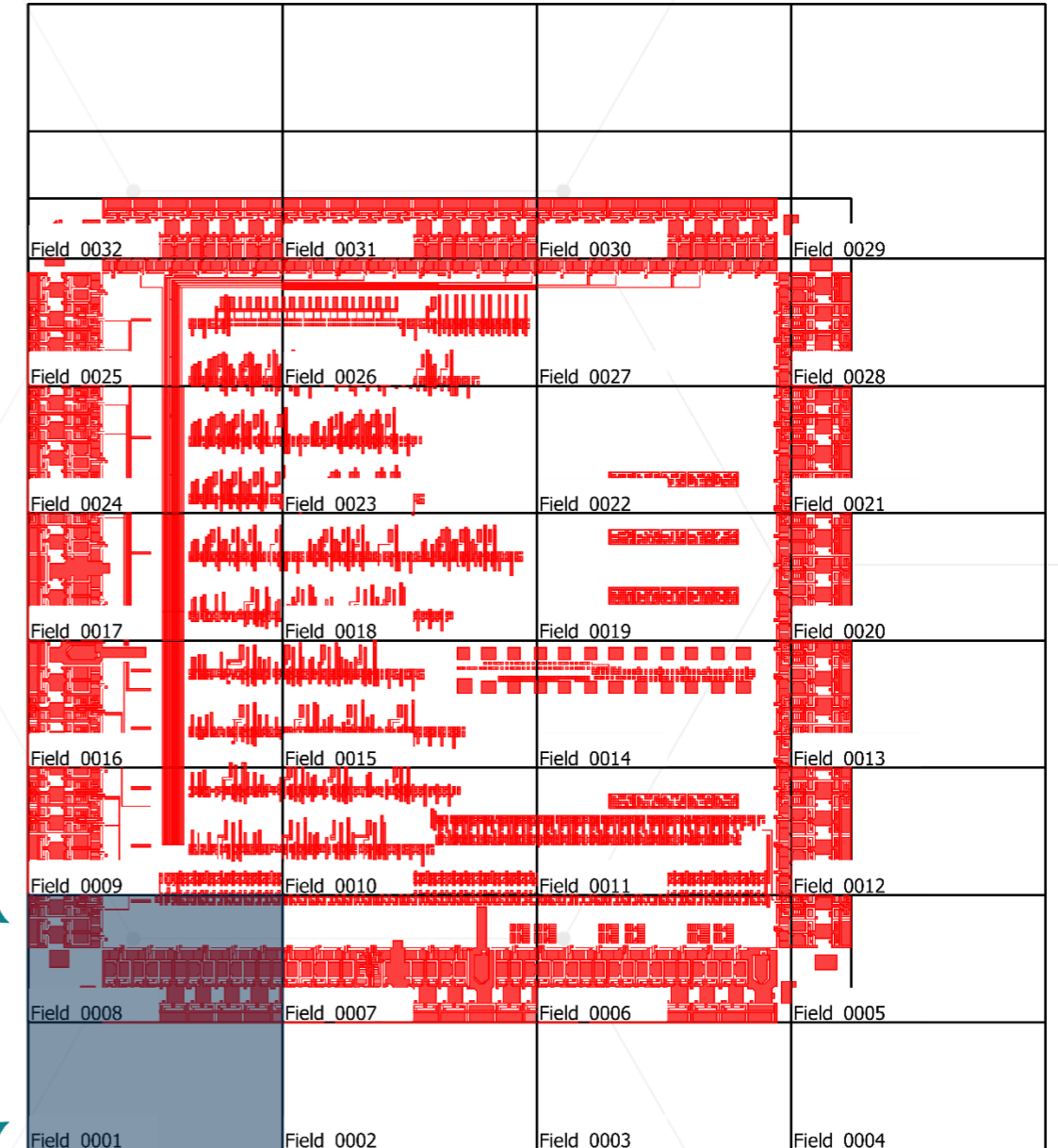
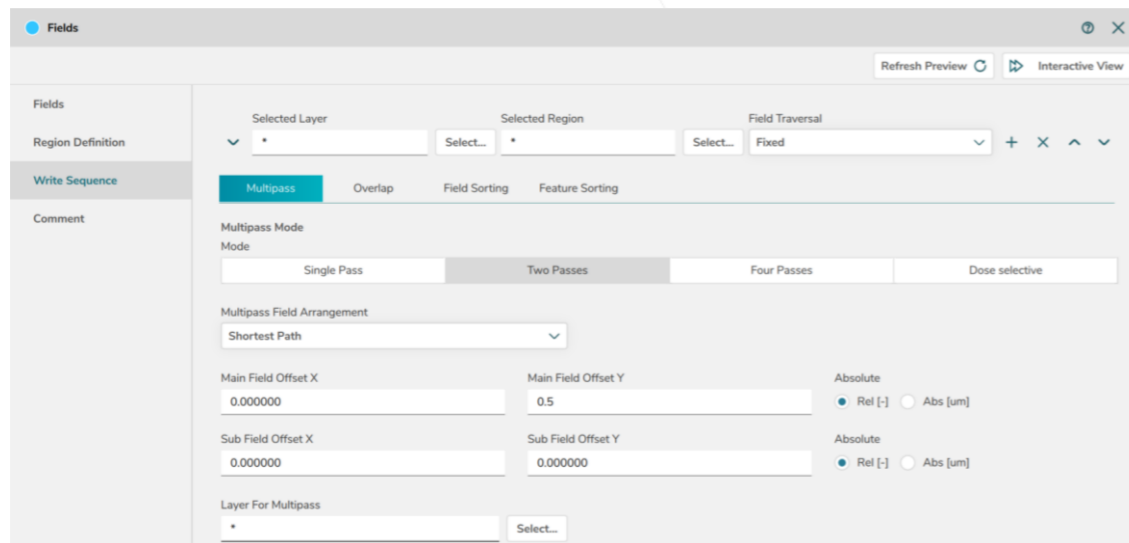
*Optional: Main or sub-field offsetting



Large layout with Field Size: 500 μm

Multipass: Two Passes

Main Field Offset Y: 0.5 Re[-] \rightarrow Half field size shift

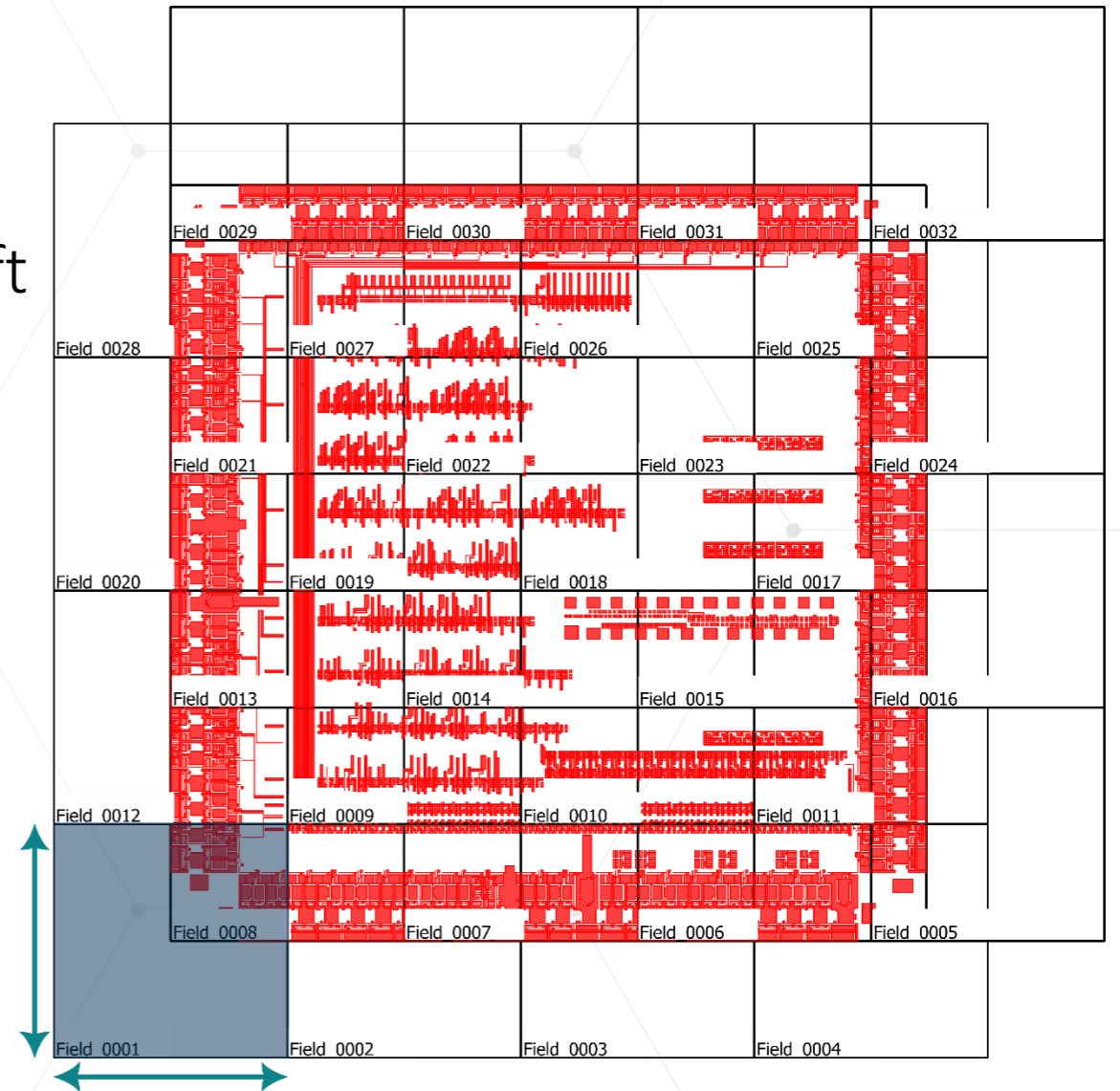
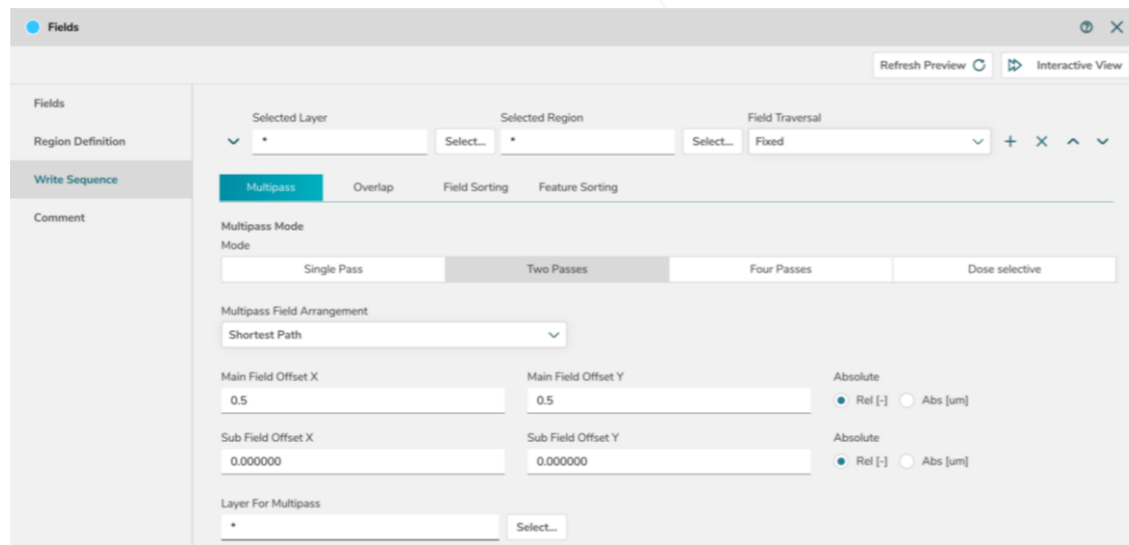


*Colour by Layer

Large layout with Field Size: 500 μm

Multipass: Two Passes

Main Field Offset XY: 0.5 Re[-]  Half field size shift



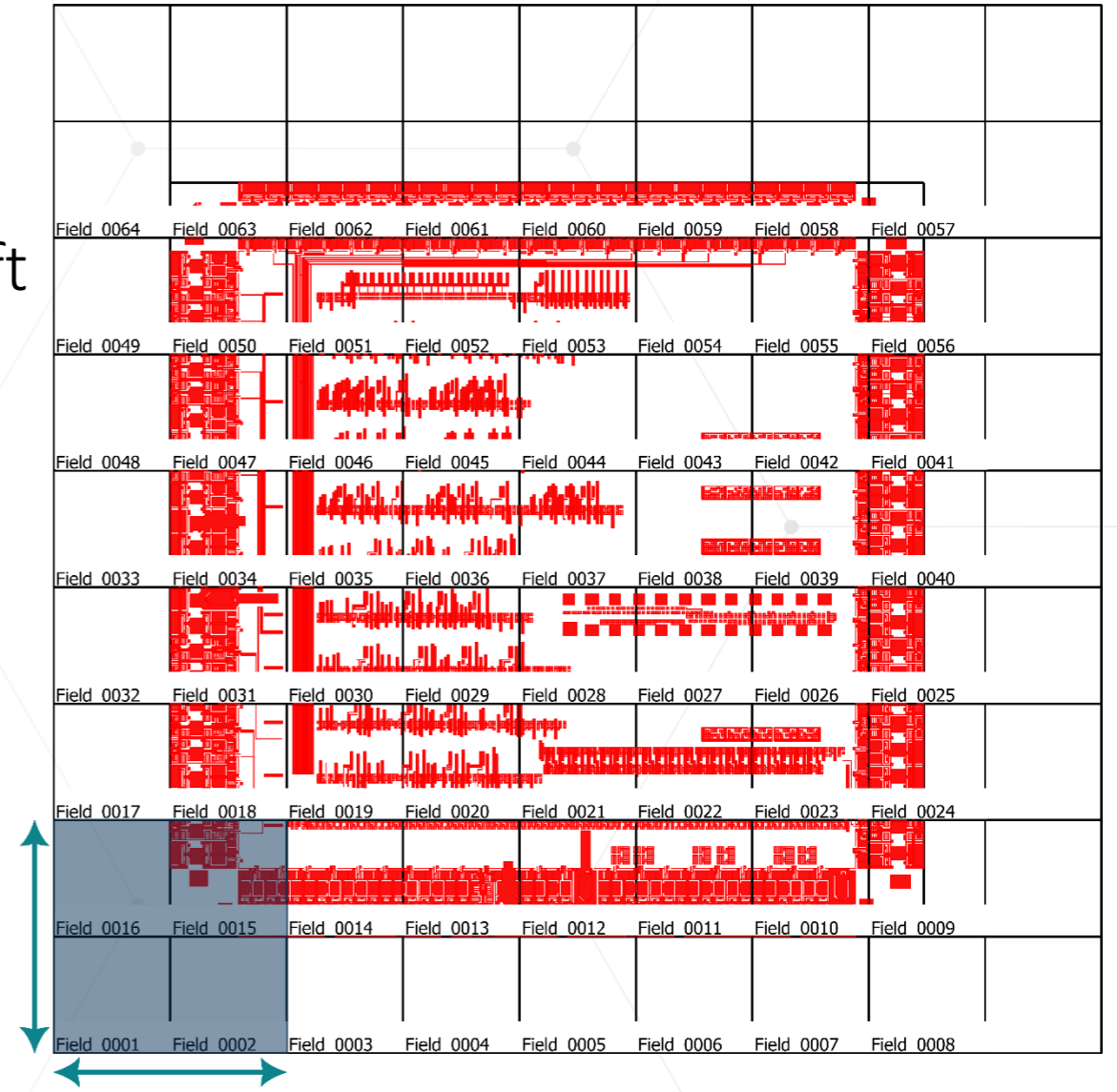
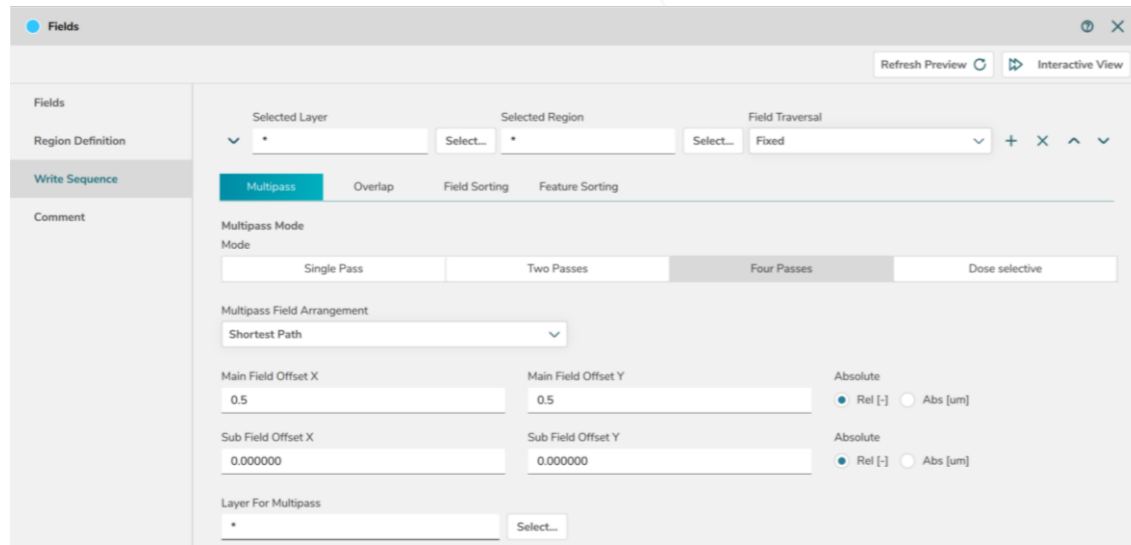
*Colour by Layer

Four Passes and XY Offset

Large layout with Field Size: 500 μm

Multipass: Four Passes

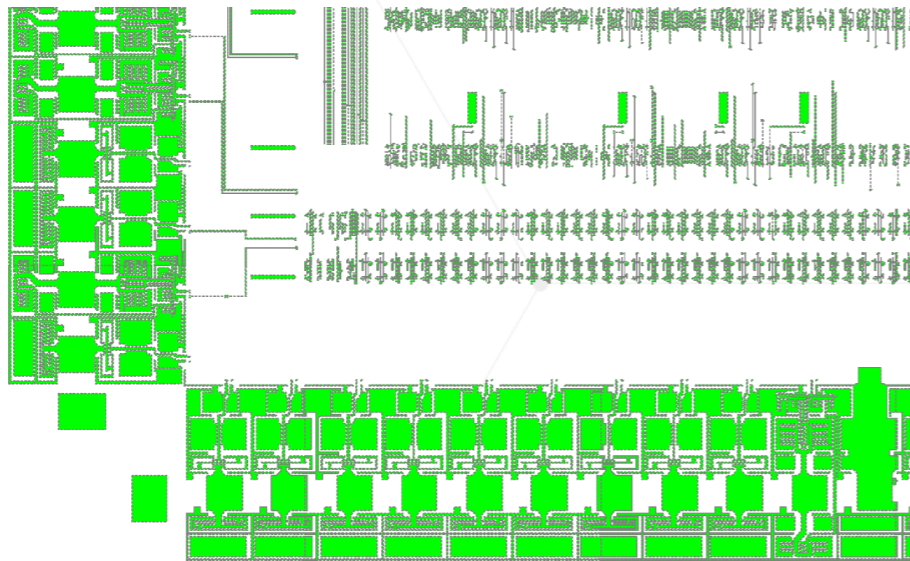
Main Field Offset XY: 0.5 Re[-]  Half field size shift



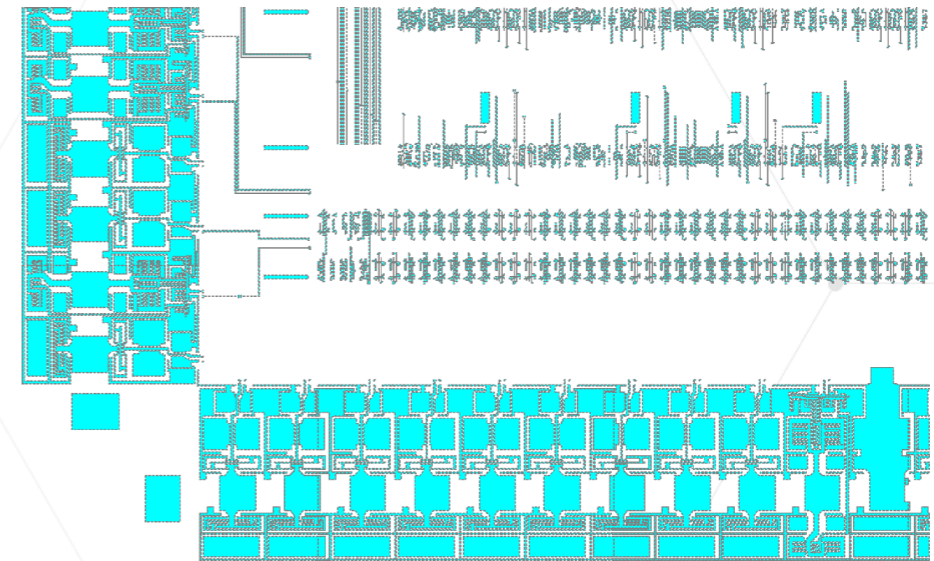
*Colour by Layer

Two and Four passes

The number of passes determines the number of exposures. BEAMER color mode *Overlay* shows this exposure difference.



Two passes



Four passes

Overlay Colors

1: [Blue]	2: [Green]	3: [Red]	4: [Cyan]	5: [Yellow]
6: [Magenta]	7: [Orange]	8: [Purple]	9: [Olive]	10: [Teal]
11: [Light Blue]	12: [Brown]	13: [Light Cyan]	14: [Pink]	15: [Purple]
16: [Light Purple]	17: [Light Green]	18: [Light Olive]	19: [Light Blue]	20: [Light Orange]

Above 20: [Grey]

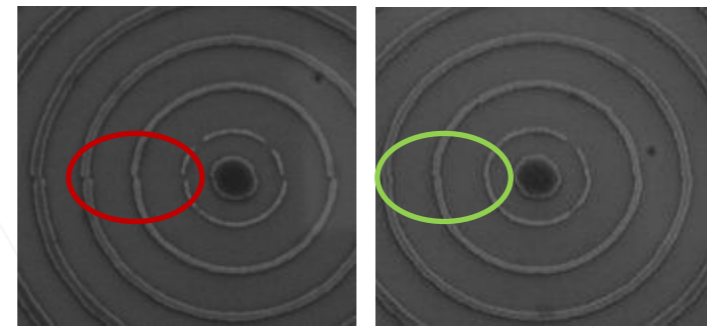
BEAMER colour code

OK Cancel

*Colour by Overlay

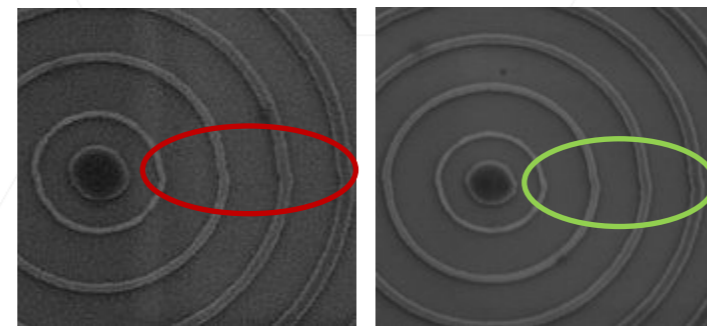
Systematic errors are averaged through offset strategies → Reduced field stitching

Single pass



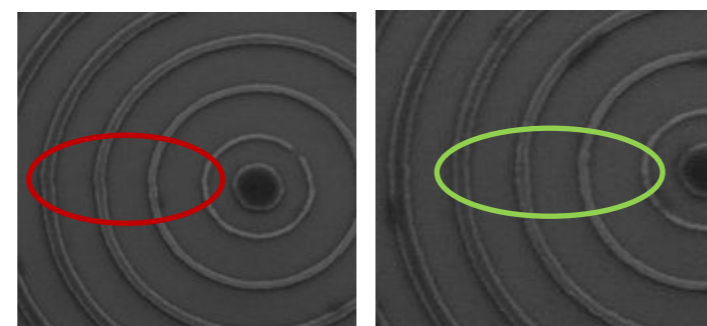
Stitching issues

4-pass w/o field shift



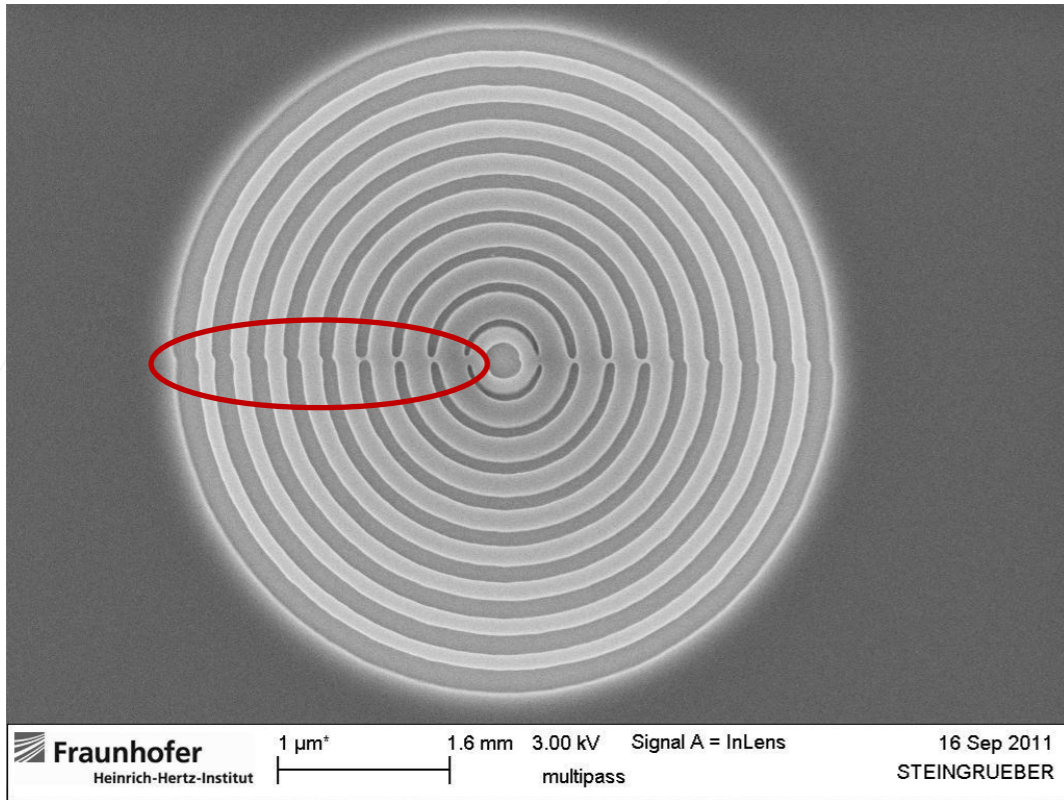
Stitching fixed but notching observed

4-pass with field shift

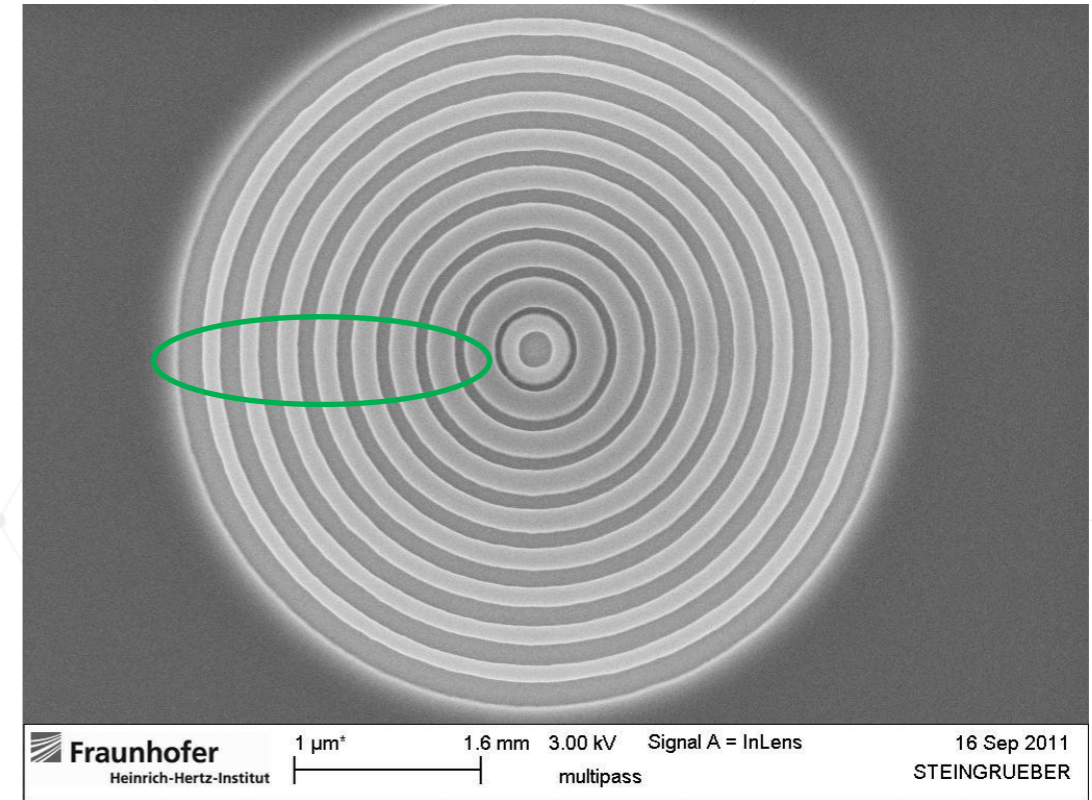


Notching reduced

Multipass in Fresnel lenses



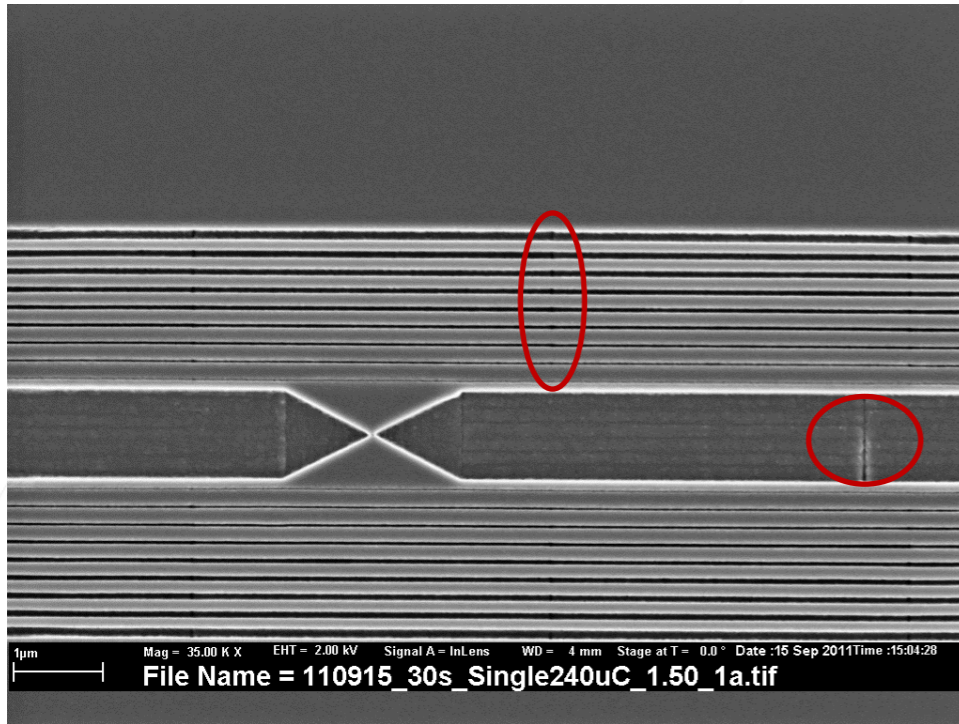
Single pass exposure with stitching errors



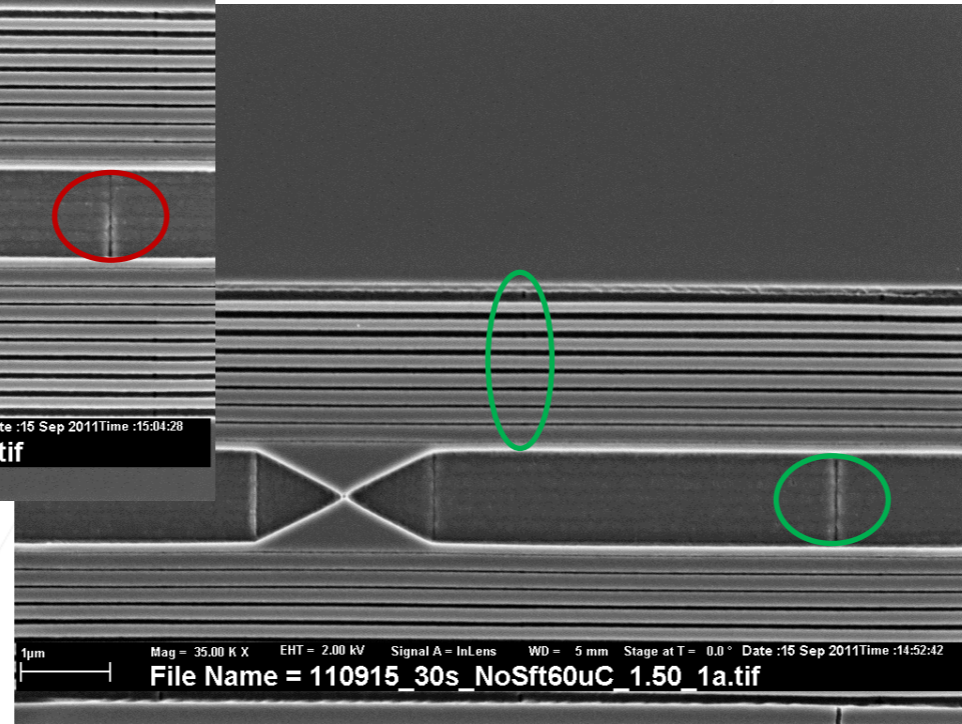
Pattern fractured with multi-pass

- Reduced Line Edge Roughness (LER) \rightarrow Improved resolution

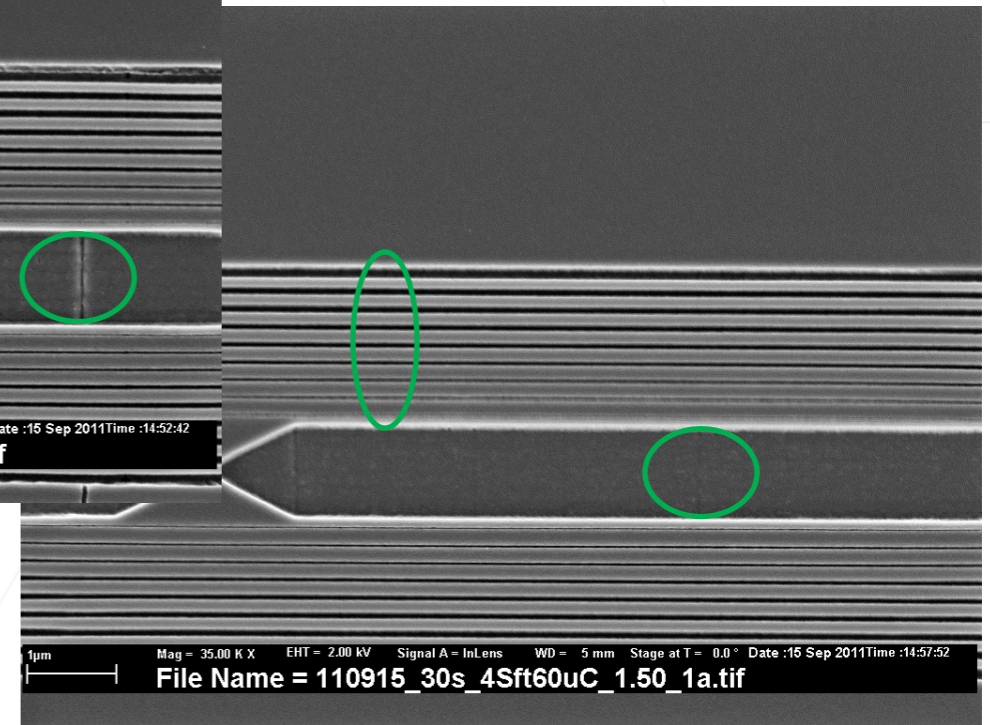
Subfield shift example



Single pass



4-passes w/o subfield offset



4-passes with subfield offset

- **Traditional Multipass results increases lithography quality**
 - Reduces Line Edge Roughness (LER) and Line Width Roughness (LWR)
 - Reduces systematic errors
 - field/subfield offset reduces stitching errors
 - Improves positional accuracy
 - field shifts compensate for field placement issues due to aberrations
 - Creates a homogenous energy distribution

- **Slower throughput**
 - Beam-on time tends to be longer
 - Exposure dose increases → Dose and current need to be manually reduced
 - Increased exposure time
 - Large file size
 - Large Overhead
 - More stage moves → more settling times

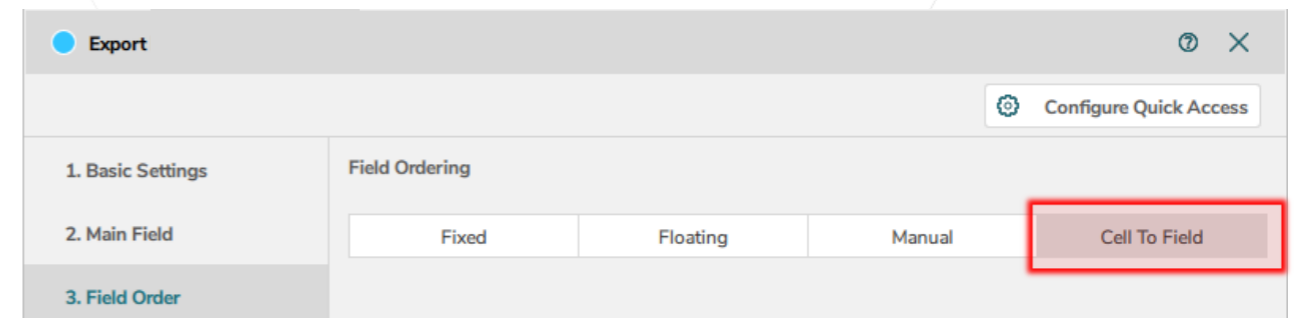
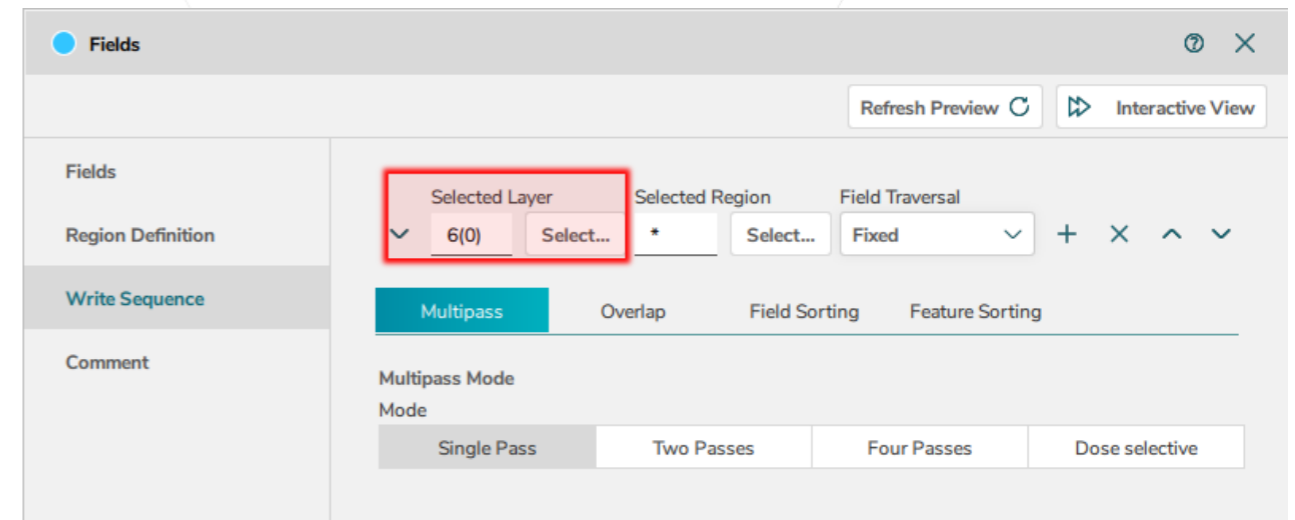
- Conventional multipass is manual
 - User needs to prepare multiple exposure files with different field size settings or shifted extend and set the multiple exposure at job-deck
 - The pattern is exposed sequentially: 1st exposure of full layout needs to be completed before 2nd starts
 - Alignment between exposures is needed to keep accuracy, meaning longer exposure time
 - Subfield shifting is not possible
 - Selective multipass is not possible

- **BEAMER Multipass**
 - The multipass is exposed within one exposure file
 - No need for multiple exposure files and special job-deck preparation
 - Writing field order is optimised to keep highest position accuracy
 - Multi-exposure without stage move is possible for high resolution
 - Subfield shifting is possible
 - Selective multipass is possible by
 - Layer
 - Dose
 - Region

- Multipass with and without field shift
- **Advanced Multipass Methods**
 - How to retrieve throughput in traditional Multipass?
 - Interstitial field blend
 - Dose overlap
- Summary

- Different applications require distinct strategies:
 - 3D structures require multipass for high doses, holograms are field size sensitive, and waveguides require field stitching mitigation
- Options are implemented for:
 - Dose dependent multipass
 - “Blending” features at field borders
 - Generic approaches
 - Merging of machine files into one file
 - Layer selective multipass

- Layer selective multipass
 - Multipass for features within a specified layer only
- Merge machine files
 - *Export Field Ordering* gets a new option to use cells as field definitions
 - Allows to merge machine files where each field is imported as a cell
 - Patterns can be split and merged in any thinkable way



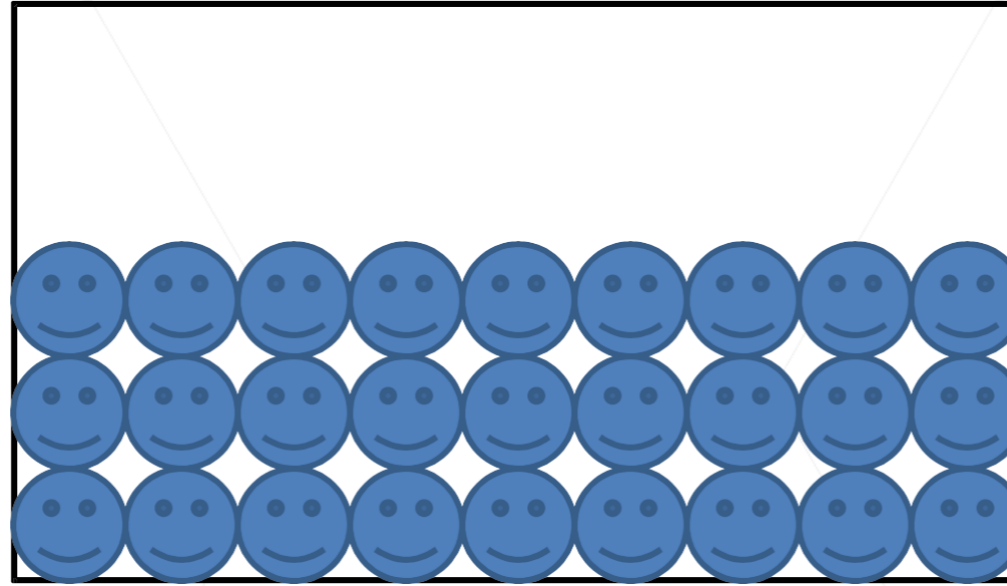
- Multipass with and without field shift
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4-passes with double Shot Pitch

- 4-passes does NOT have to increase the beam-on time iff

➔ The spot pitch is doubled

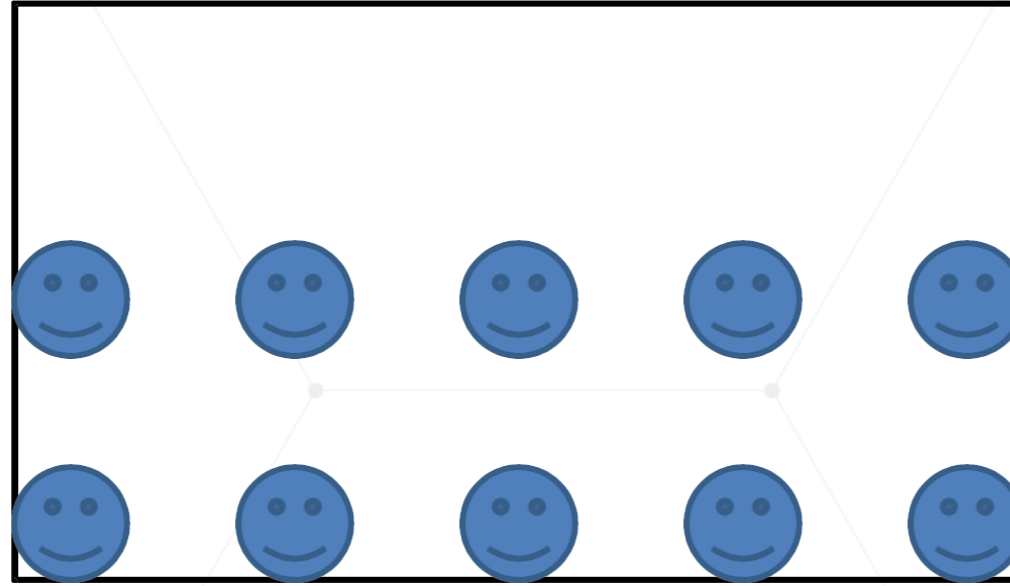
- Doubling the spot pitch does NOT decrease resolution
 - Results in the same filling as single pass



Single Pass Fill

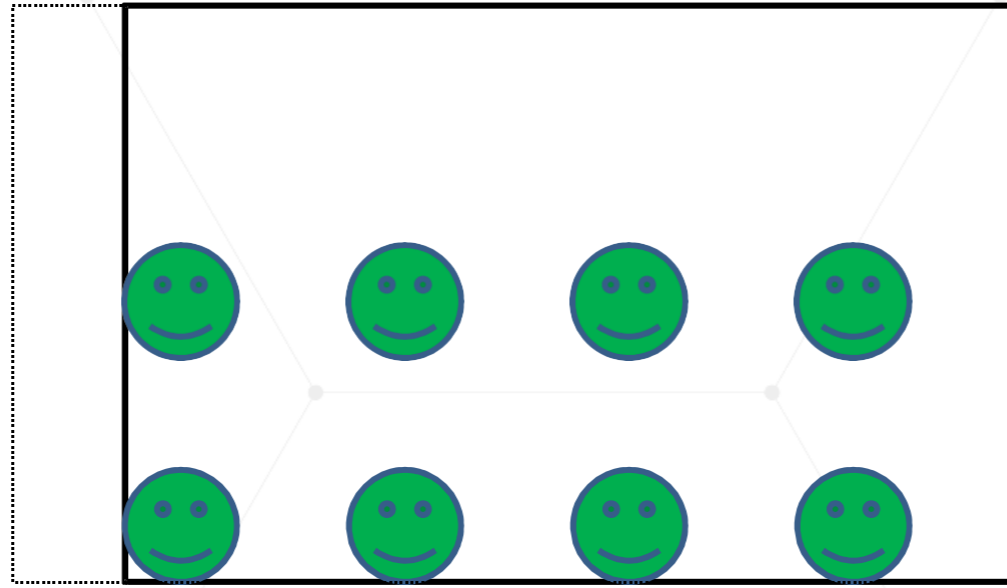
Single pass has a continue filling approach of a feature

Multipass subfield strategy



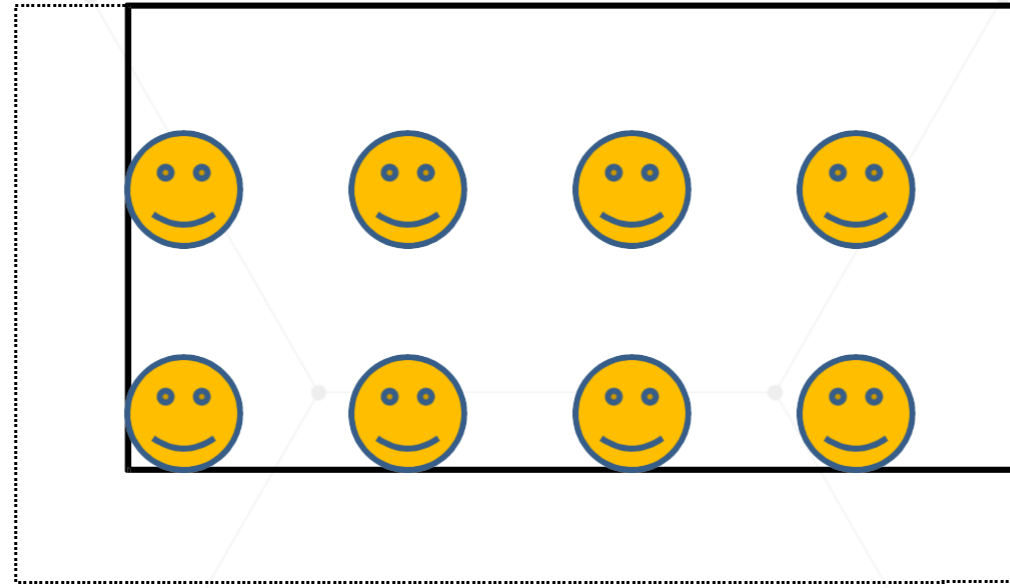
4-Passes – 1st Pass

4-passes with subfield shift results in the same pixel filling as single pass approach



4-Passes – 2nd Pass

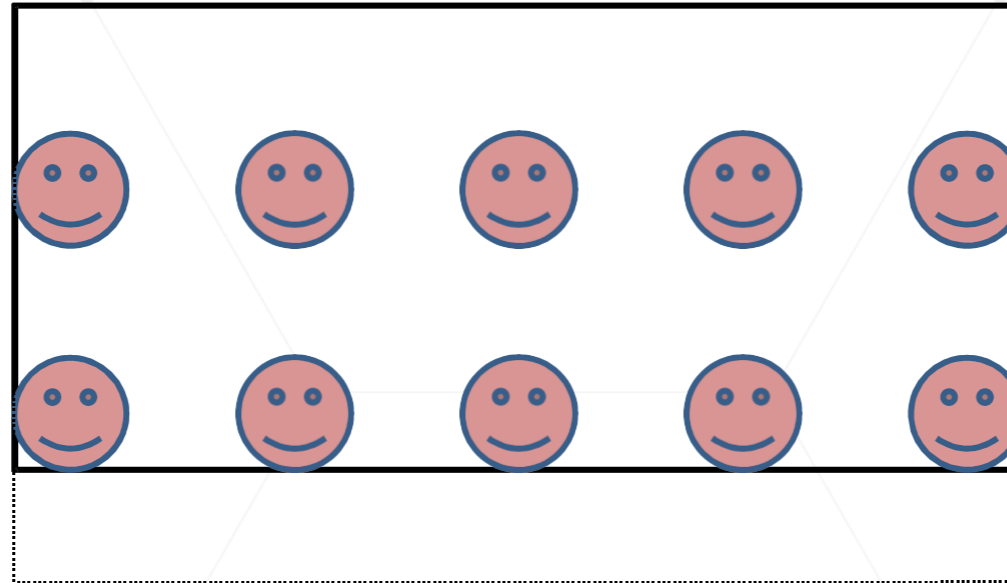
4-passes with subfield shift results in the same pixel filling as single pass approach



4-Passes – 3rd Pass

4-passes with subfield shift results in the same pixel filling as single pass approach

Multipass subfield strategy



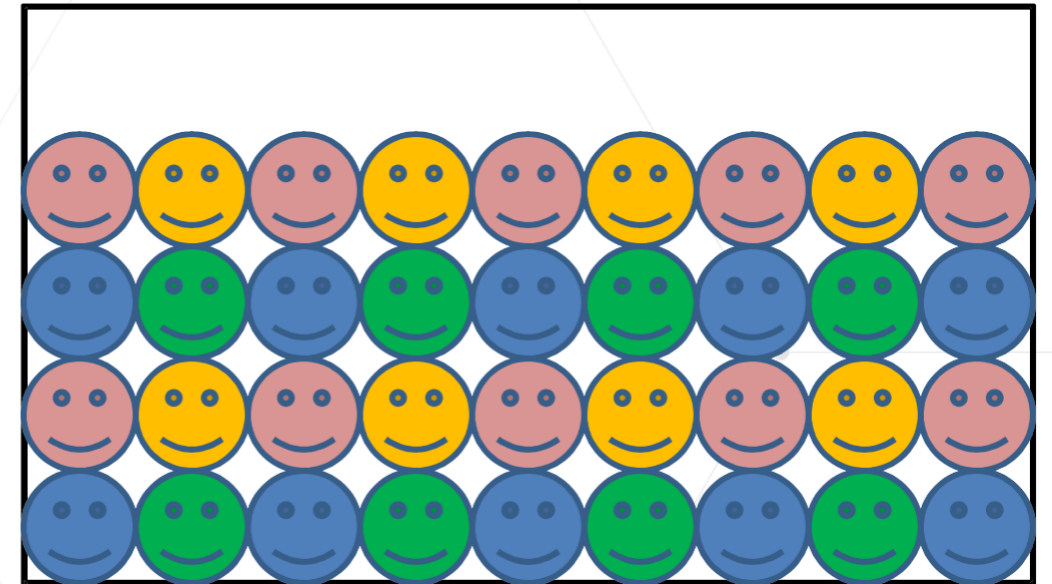
4-Passes – 4th Pass

4-passes with subfield shift results in the same pixel filling as single pass approach

Multipass subfield strategy

4-passes with subfield shift results in the same pixel filling as single pass approach

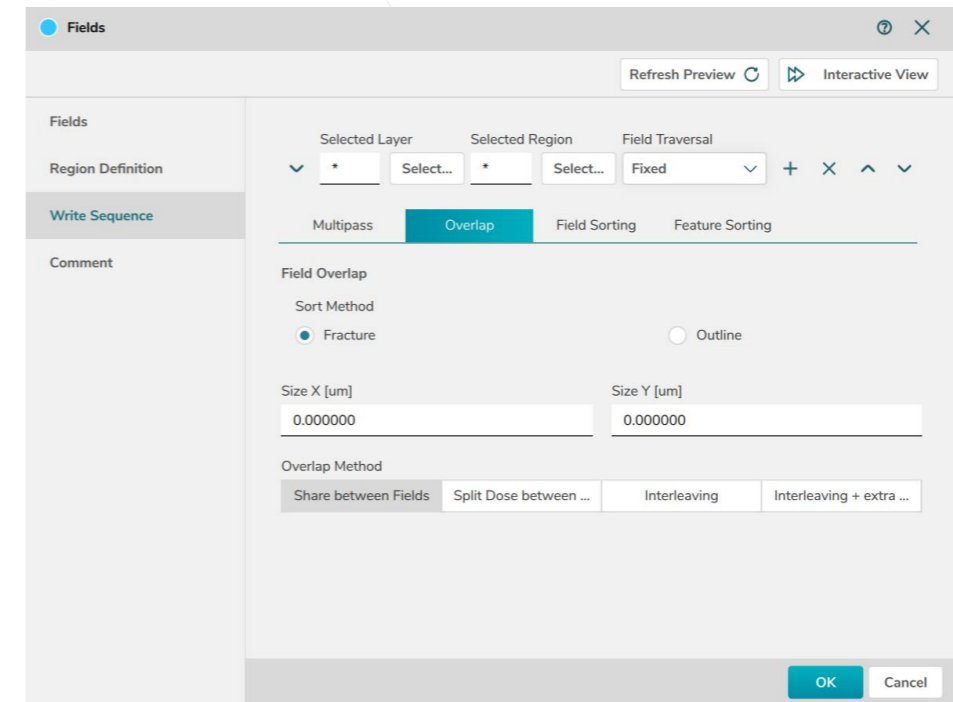
- Excepting additional field movements, this results in the same throughput as single pass
- Carries all the benefits of averaging statistical / systematic errors



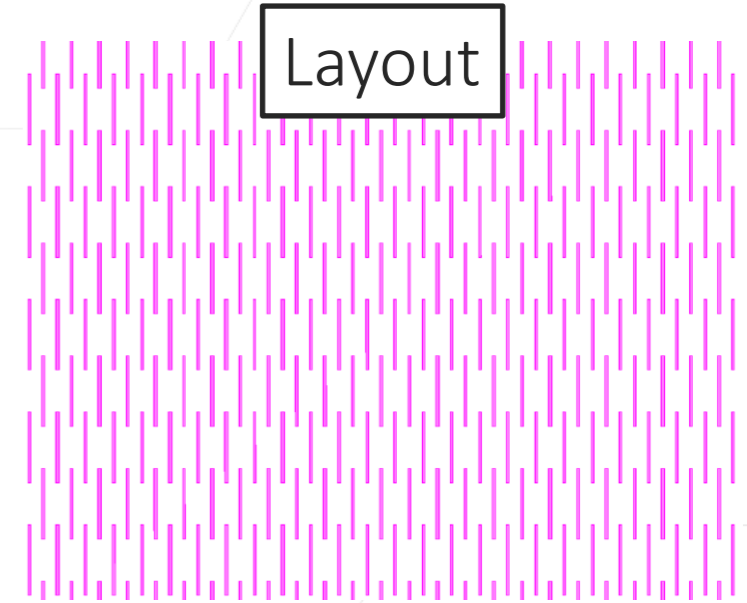
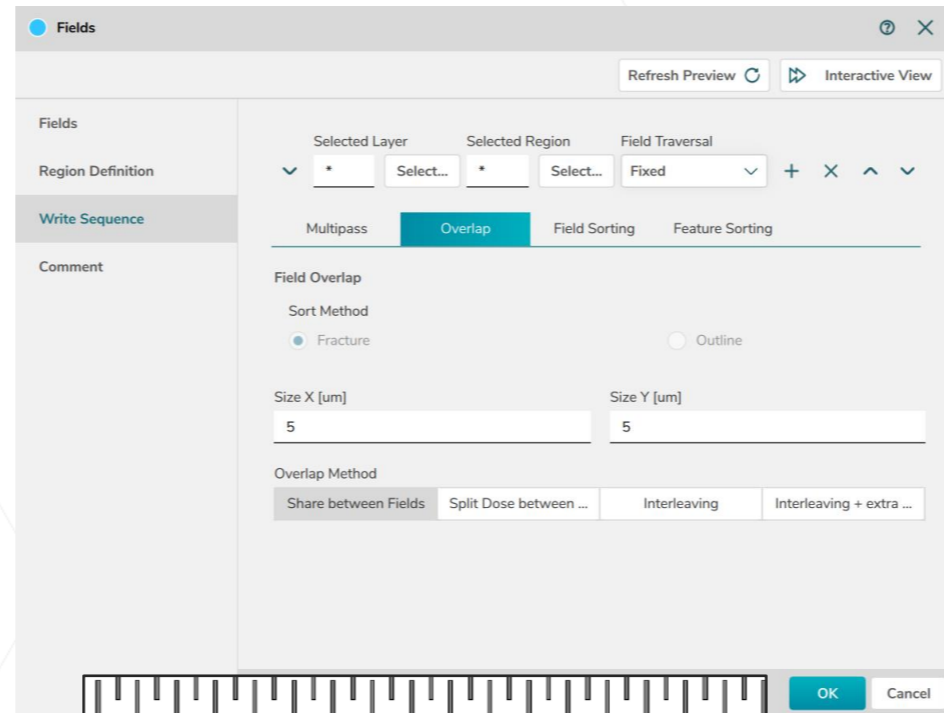
4-Passes – Final

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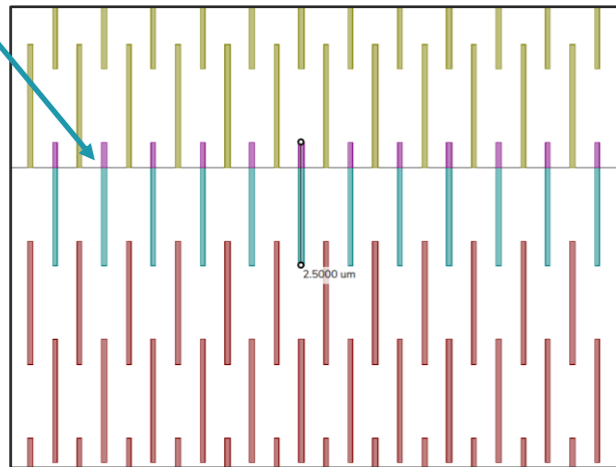
- Using single pass for features inside a field
 - Enables *Sort Method*
 - *Fracture*
 - *Outline*
- For Single, Two, Four-passes and Dose selective
 - Overlap methods available
 - *Share between Fields*
 - *Split Dose between Fields*
 - *Interleaving*
 - *Interleaving + extra field*



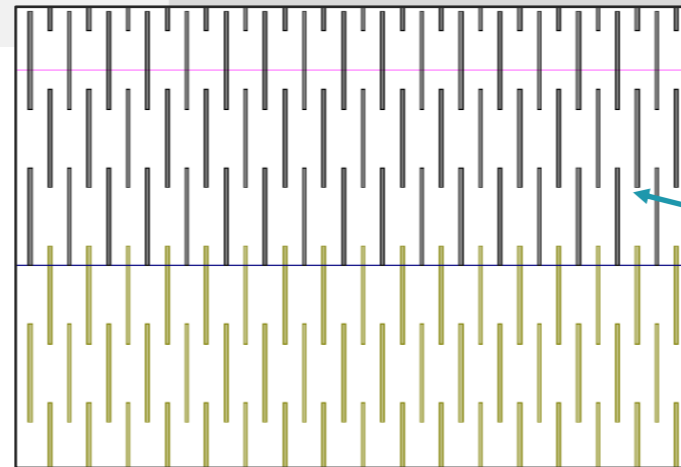
- **Field Overlap**
 - Size XY
 - Overlap Method
 - Share Between Fields



Potential stitching



Overlap = 0

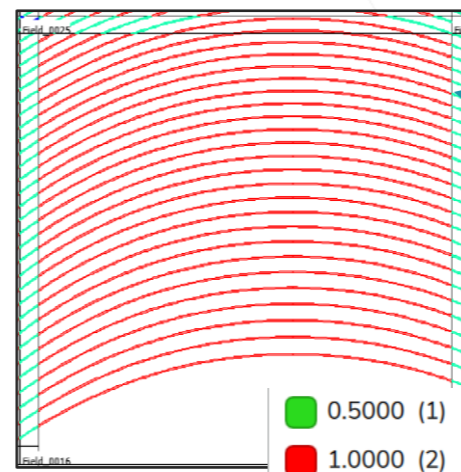
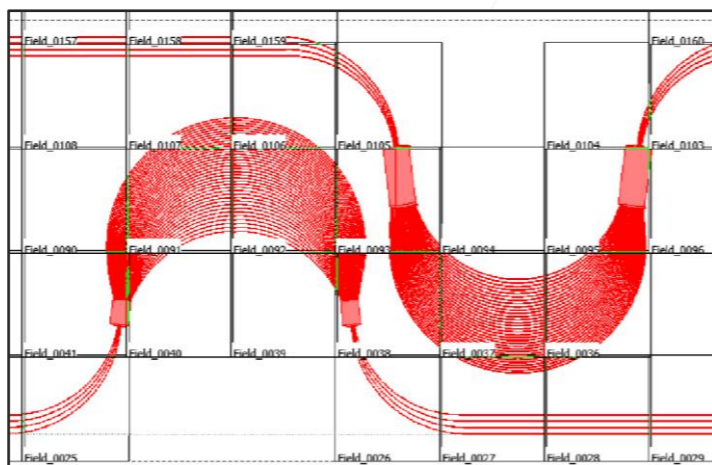
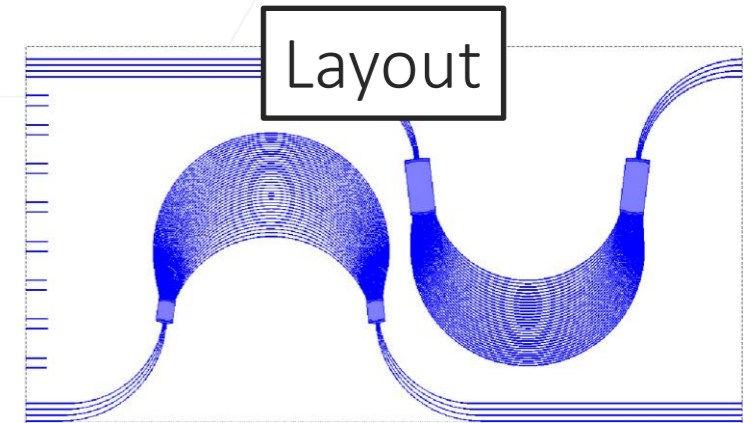
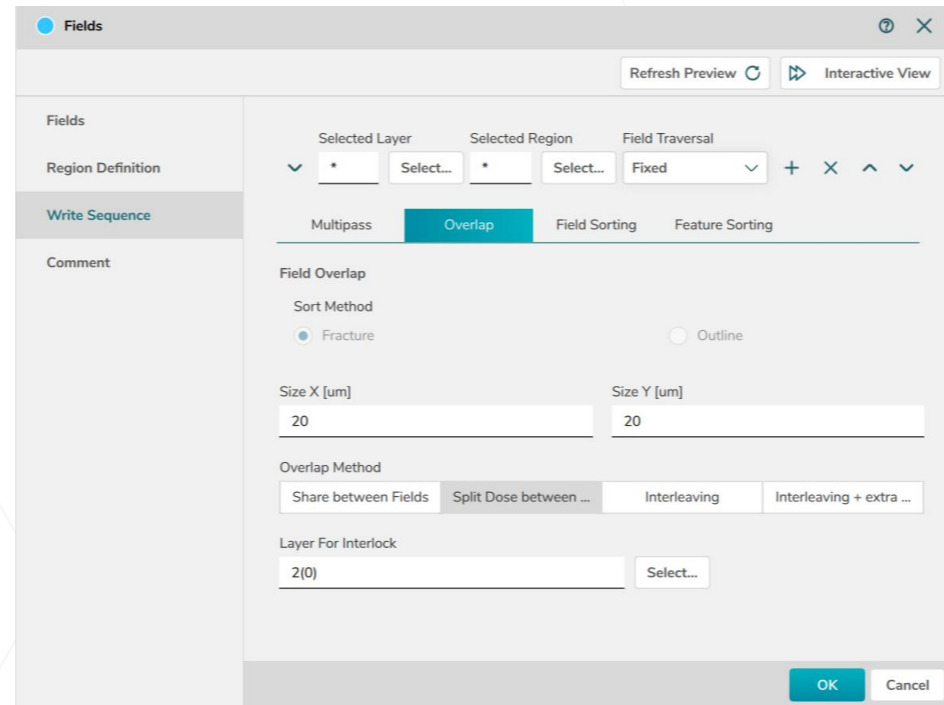


Overlap = 5 µm

Stitching avoided

*Color by Cell

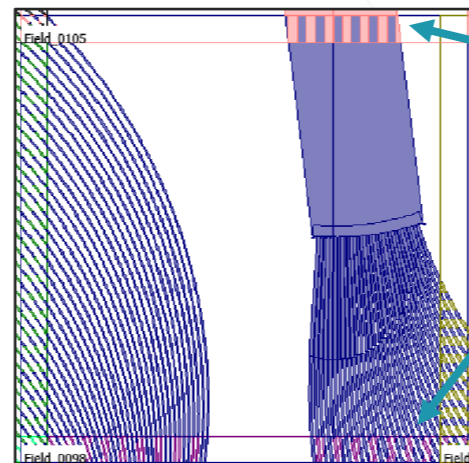
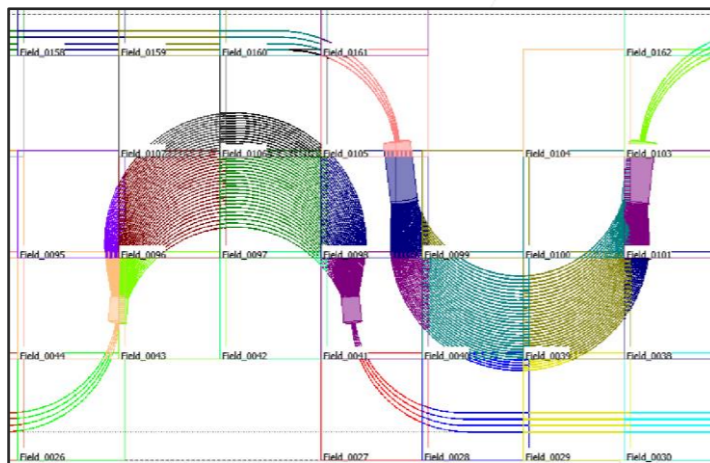
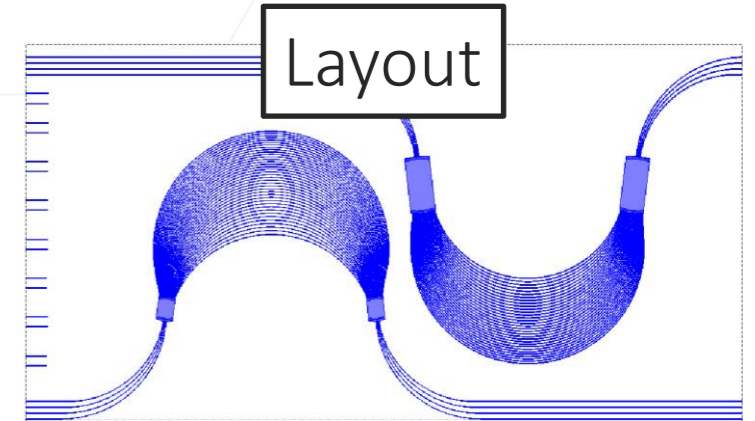
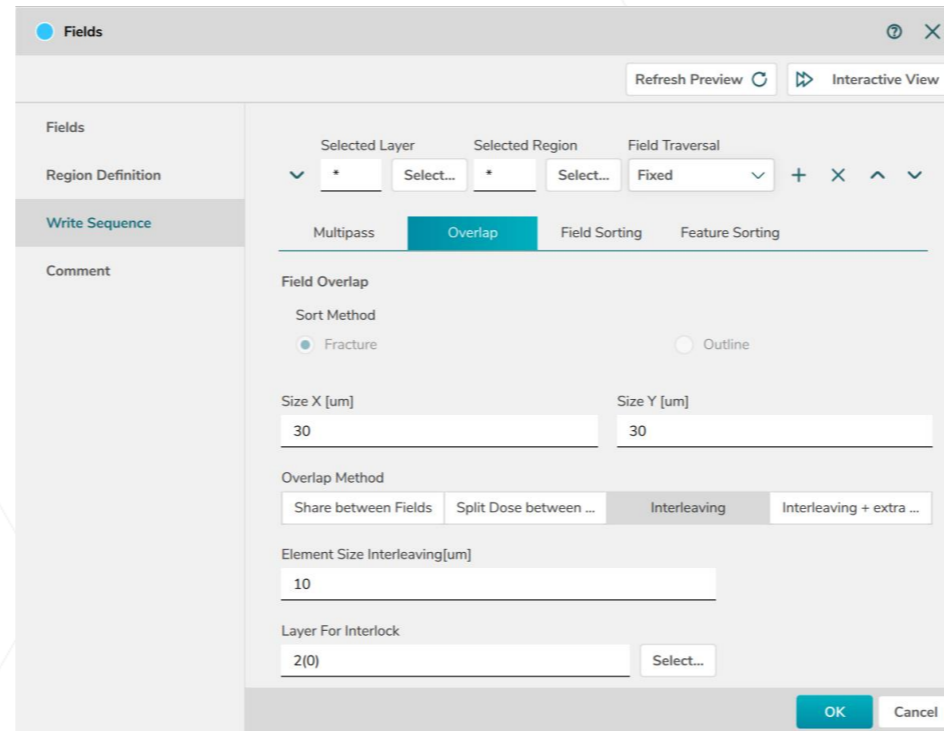
- Field Overlap
 - Size XY
 - Overlap Method
 - Split Dose between Fieds



Shared dose area

*Color by Dose

- Field Overlap
 - Size XY
 - Overlap Method
 - Interleaving



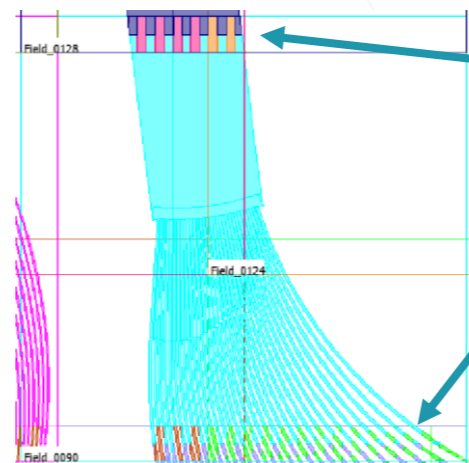
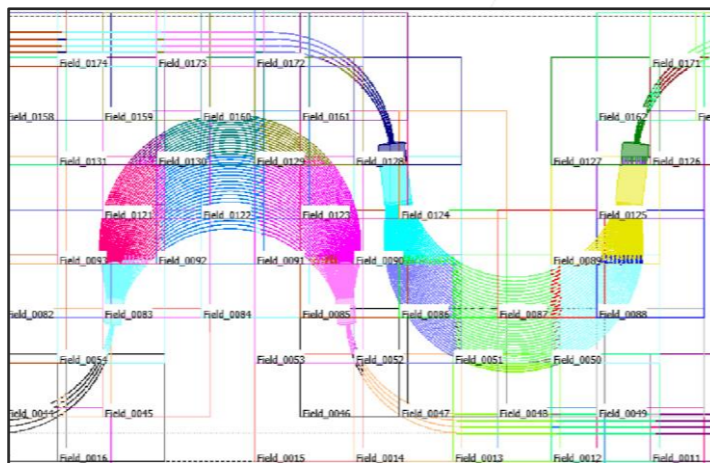
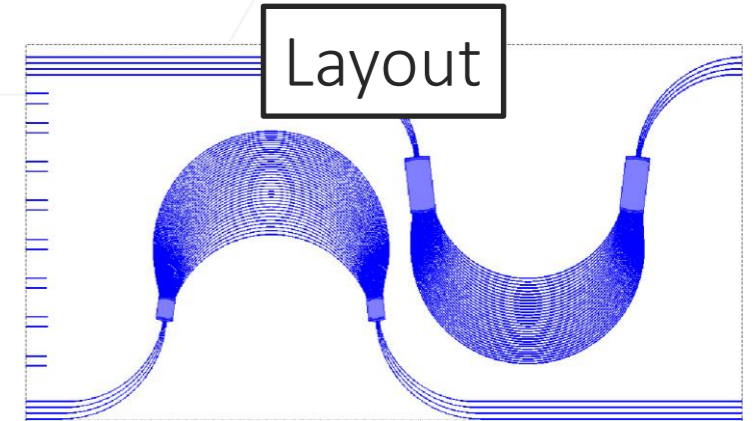
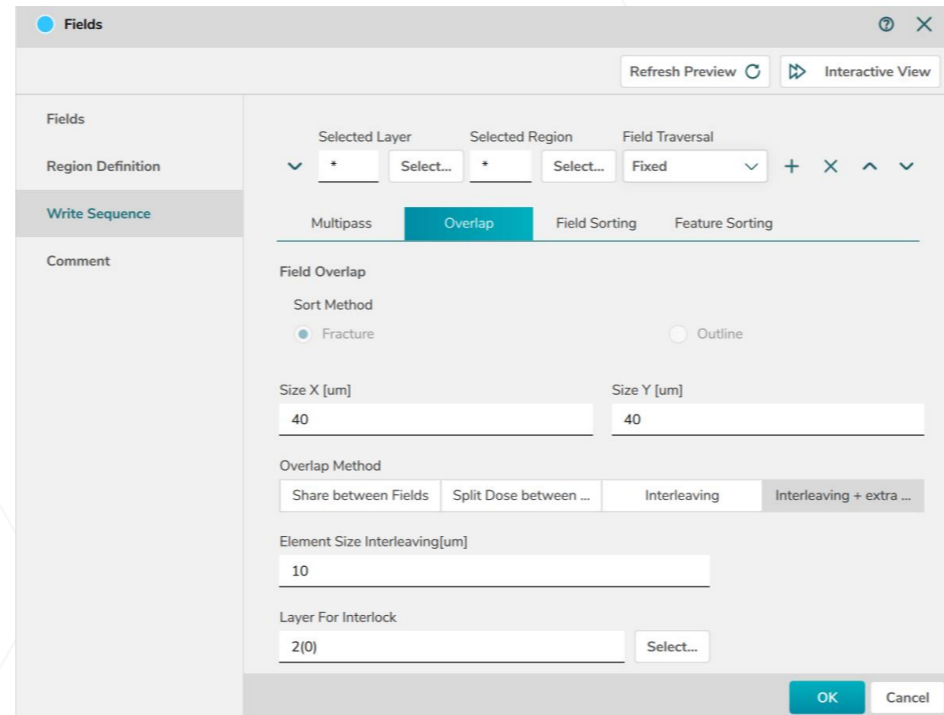
$30 \times 10 \mu\text{m}^2$

Field overlap is minimum 2x size interleaving

*Color by Cell

- Field Overlap

- Size XY
- Overlap Method
 - Interleaving + extra Field



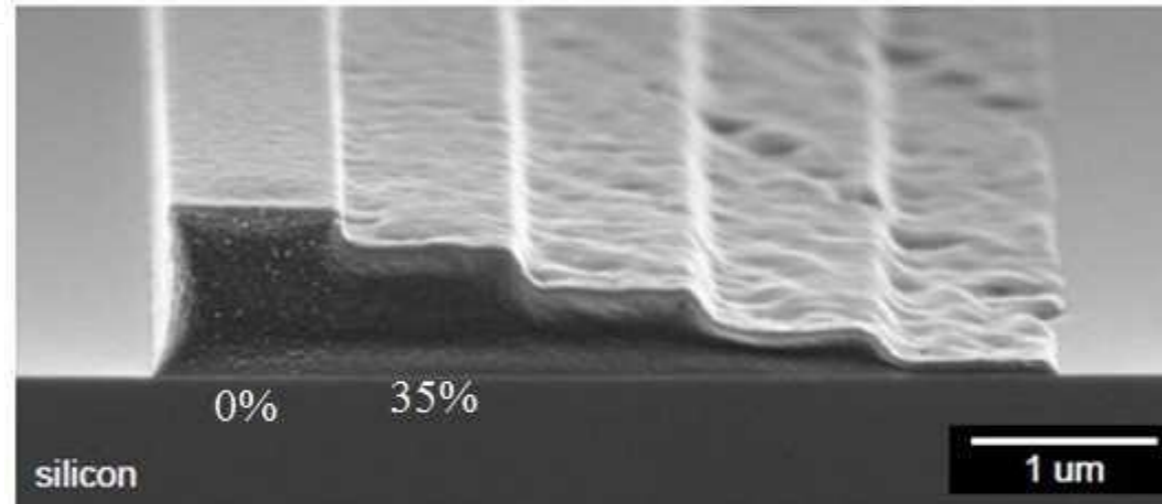
Field overlap is a multiple of 4x size interleaving

*Color by Cell

- All pattern data is *Single Pass* exposed
 - ➔ Base dose stays the same
 - ➔ Frequency range stays the same
 - ➔ Beam current stays the same
 - ➔ Exposed area is equal to the single pass
 - Overall exposure time is comparable to single pass

- Multipass with and without field shift
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What about 3D structures?

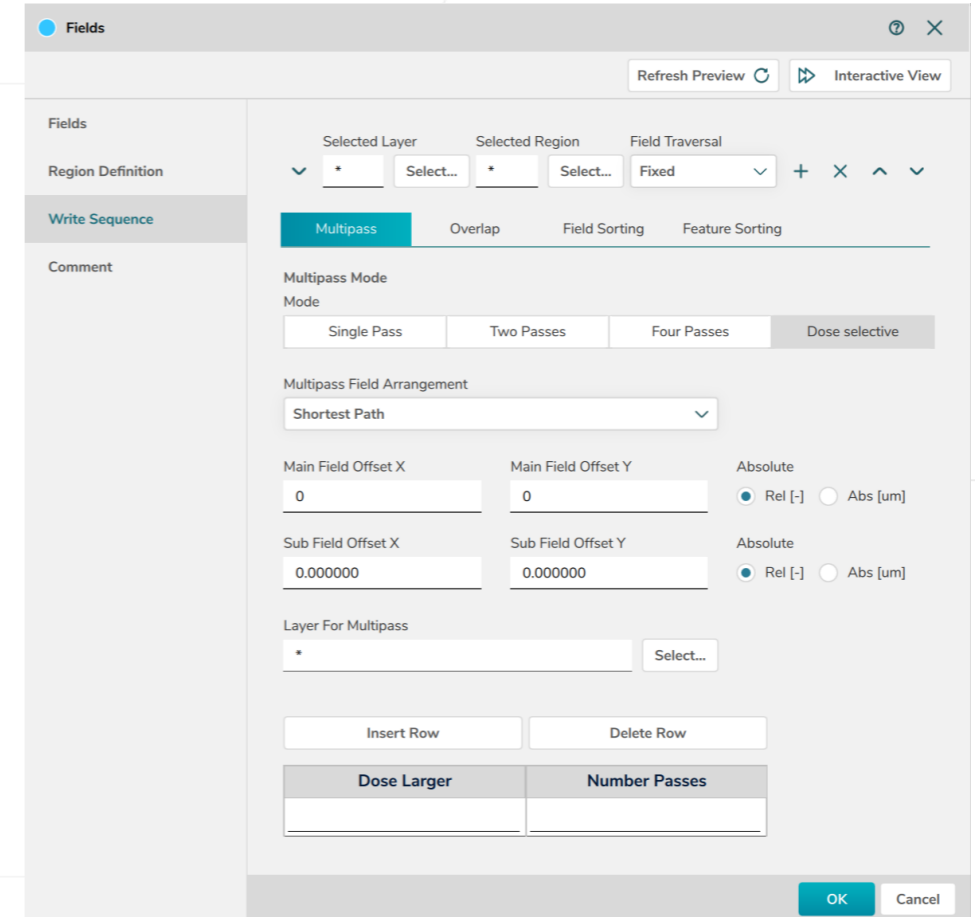


- Larger Dose (bottom steps) exhibit more noise
- **BEAMER** does *Dose selective* multipass

Dose Multipass Example

Dose Class	Original Dose	Adapted Dose	#Passes
0	1,031772	1,031772	1
1	1,219605	1,219605	1
2	1,441632	1,441632	1
3	1,704079	0,8520395	2
4	2,014304	1,007152	2
5	2,381005	1,1905025	2
6	2,814463	0,938154333	3
7	3,326832	1,108944	3

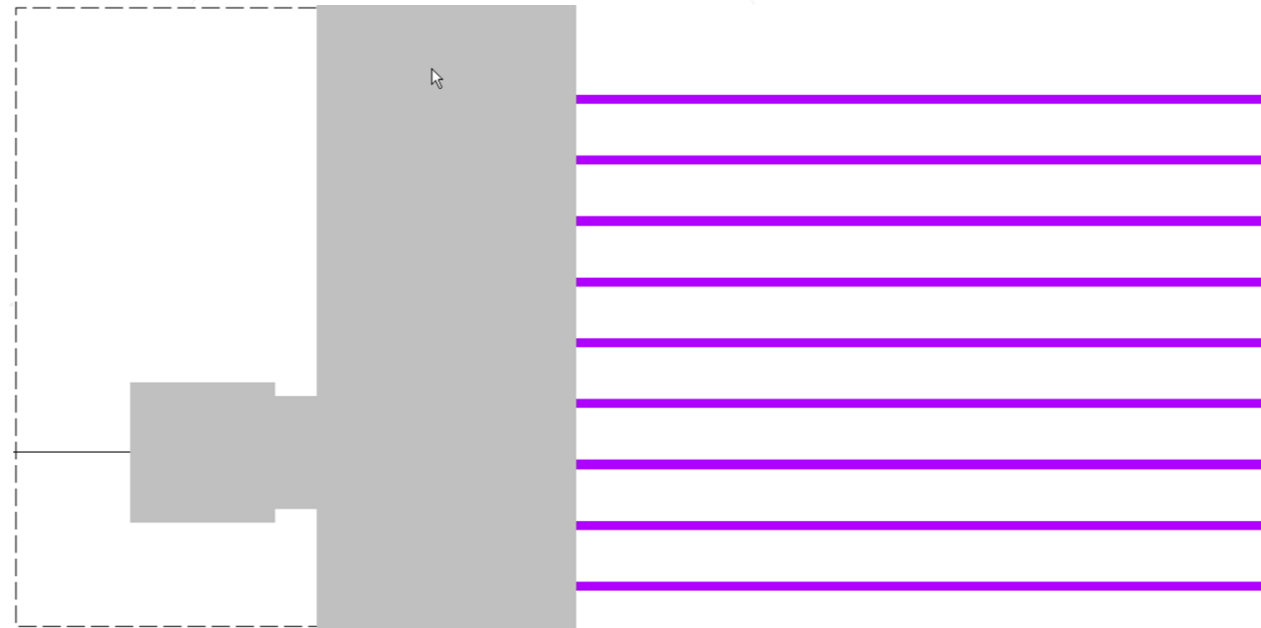
Approximated values
Multi-exposure Sequence



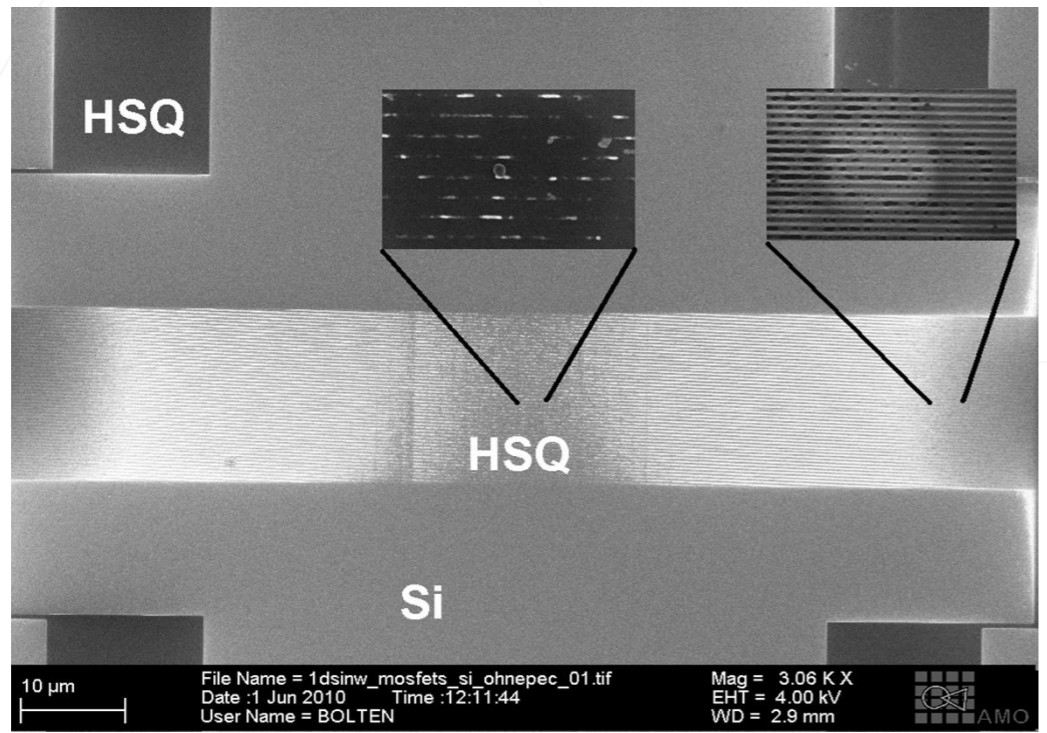
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- Traditional multipass improves LER, LWR, field- and subfield-stitching issues at the expense of throughput
- Improving the throughput while maintaining the benefit of multipass is possible using
 - 4-pass at 2x shot pitch for photonic applications
 - Interstitial field blending for large area high resolution devices
 - Dose multipass for 3D- and nano-structures
 - Generic approaches that allow to split the pattern in any thinkable way

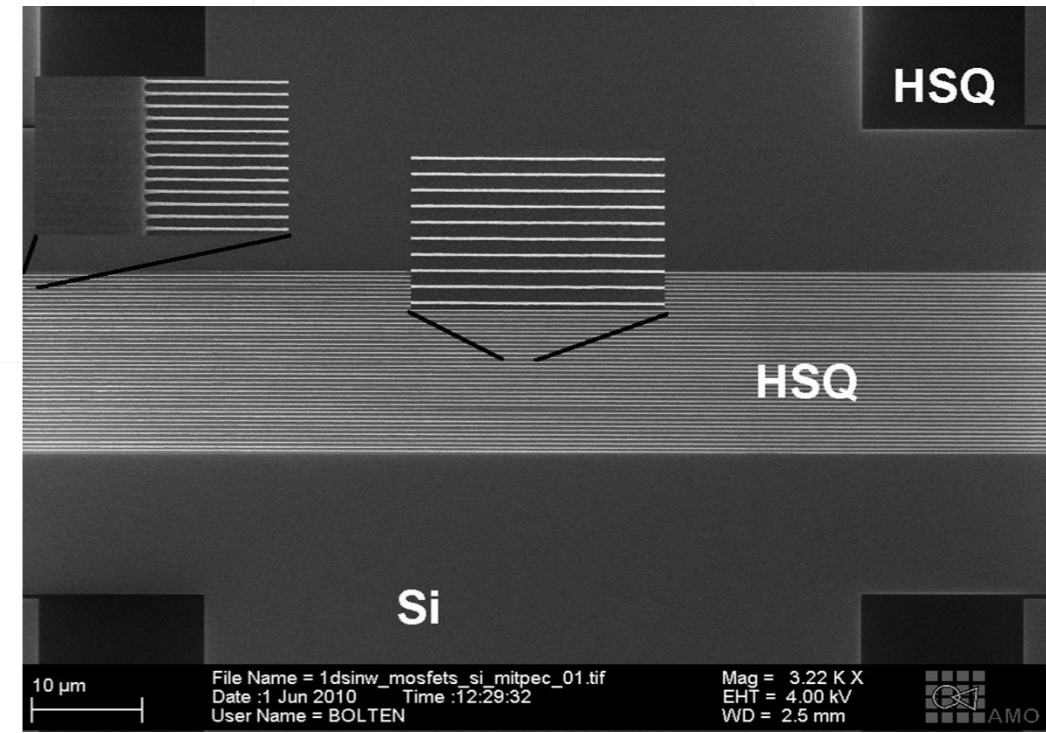
- The following work from AMO shows the benefit of PEC in conjunction with Multipass
 - PEC is needed to correct for different densities
 - Wires have small density, pads a large density
 - Multipass is needed to average statistical noise



No PEC

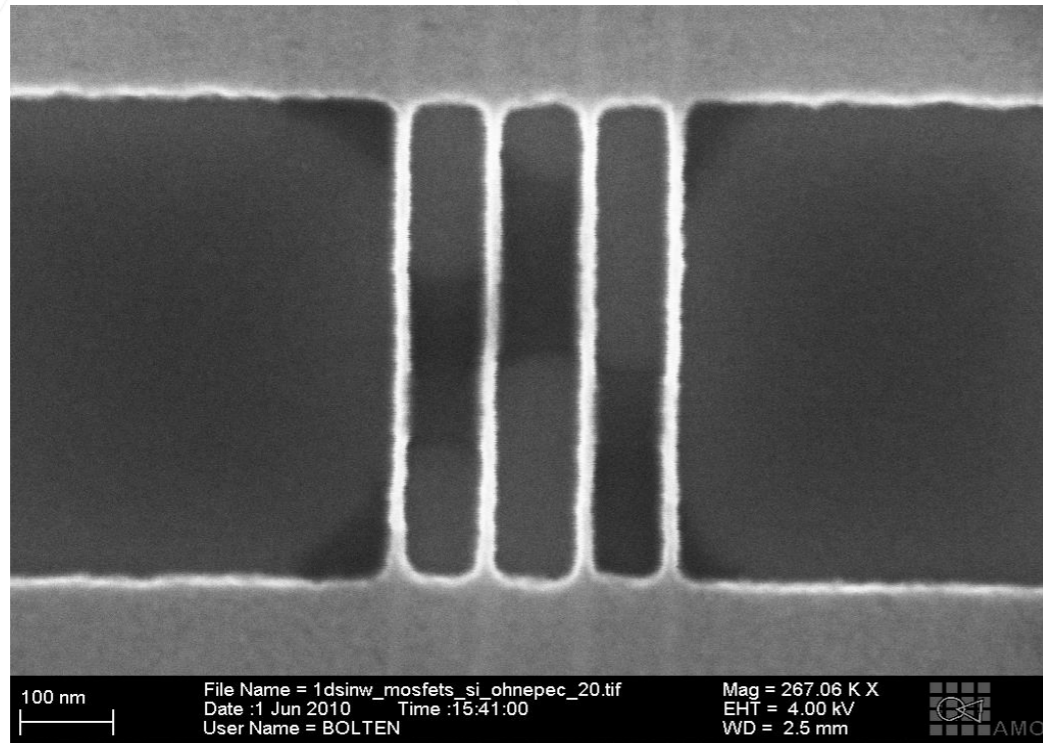


PEC exposure

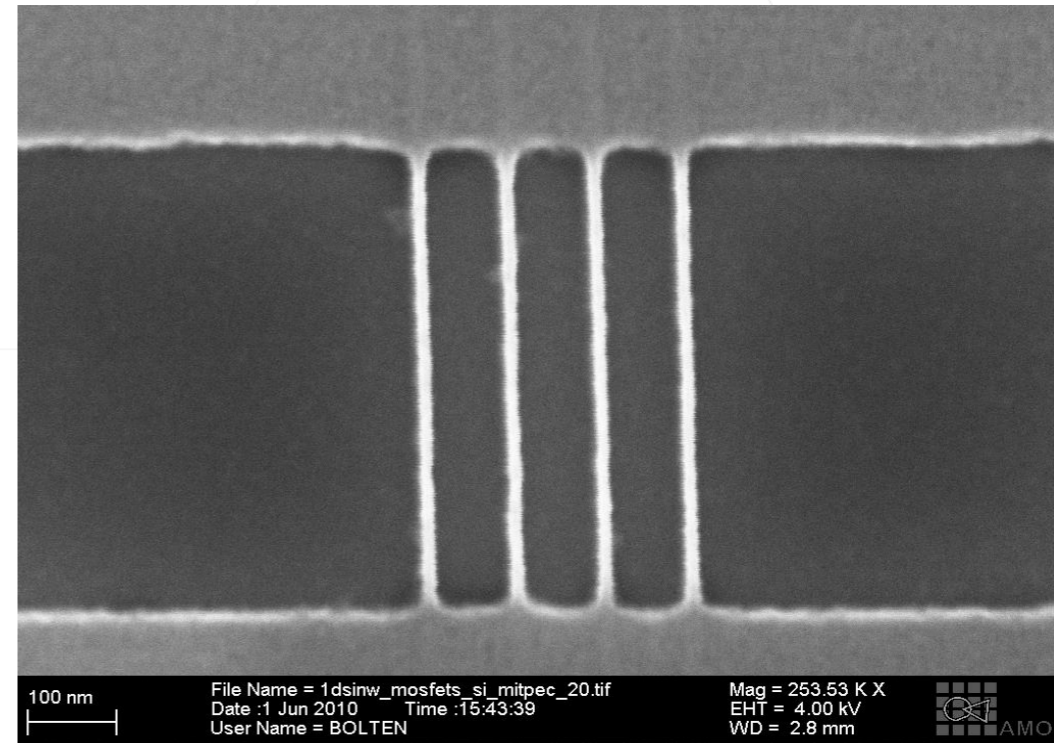


PEC mandatory for fabrication of dense nanowire arrays

Single Pass

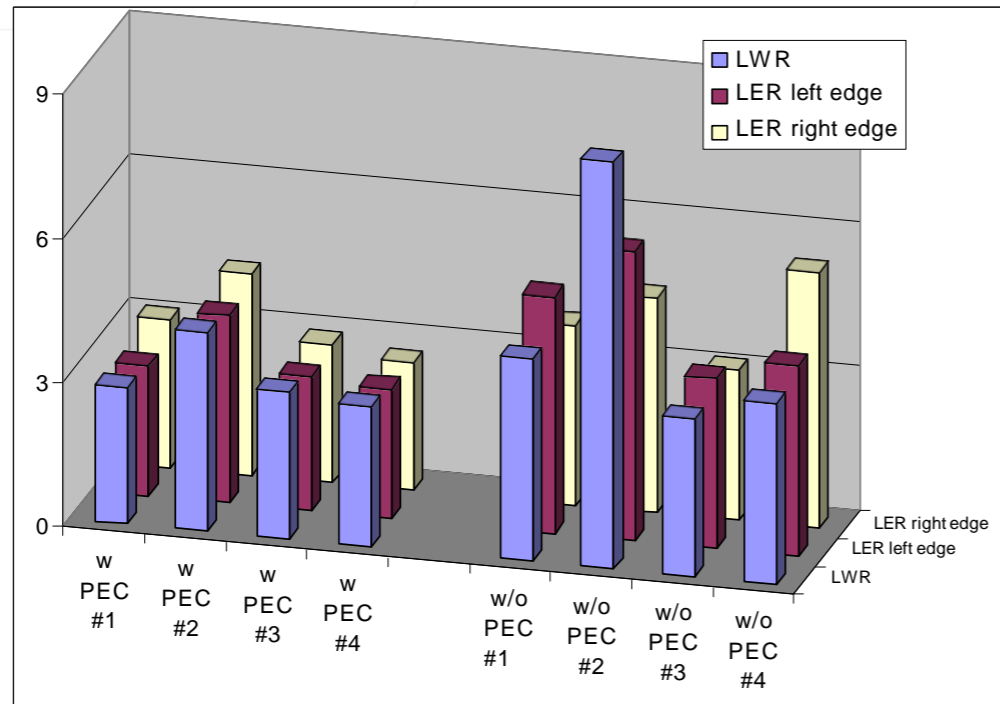


Multipass



Multi-pass exposure strategy can significantly reduce both LER and LWR

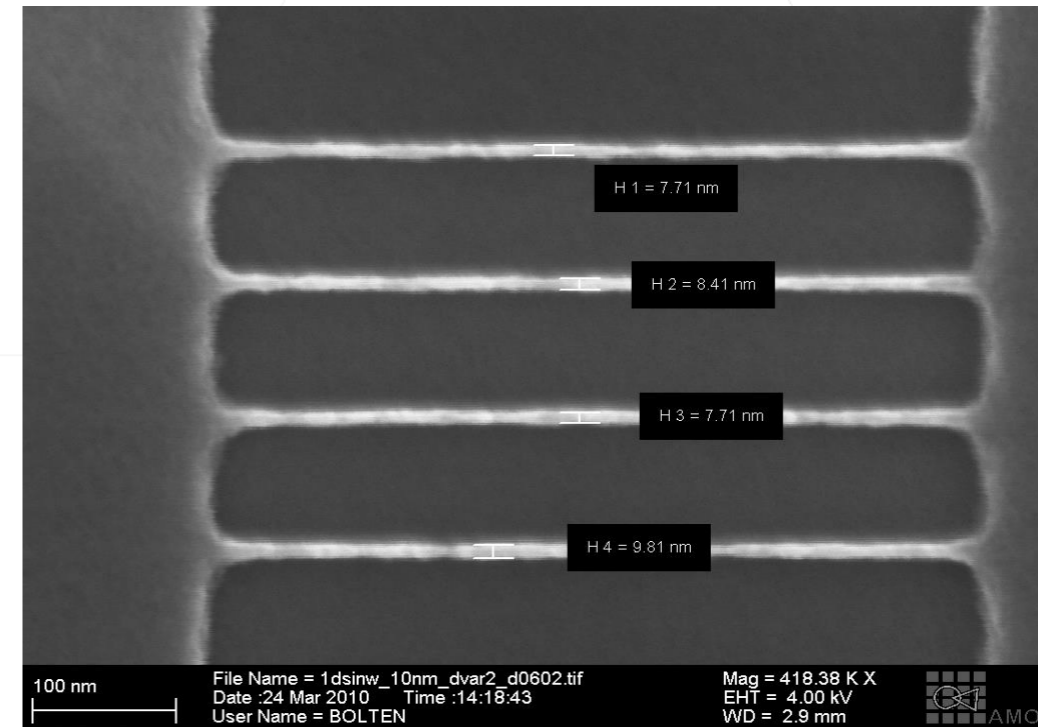
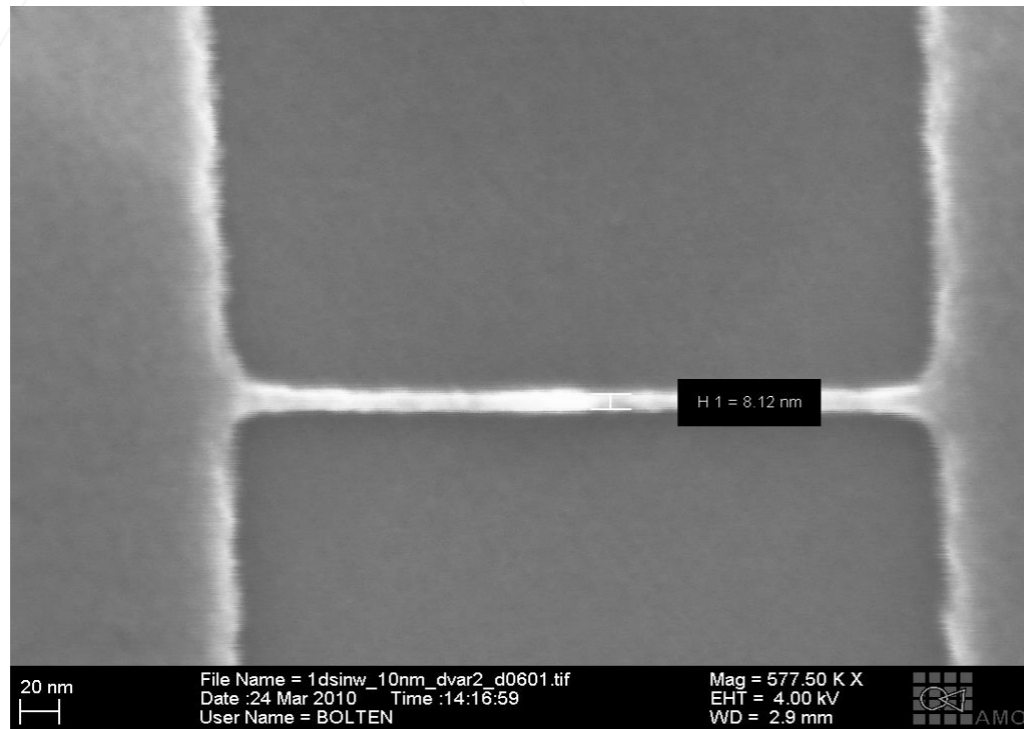
Analysis of SEM image data



- LER
 - Single pass: ~4nm,
 - Multi-pass: ~3nm
- LWR
 - Single pass: ~5nm
 - Multi pass: ~3nm

With multi-pass exposure strategy ~25% less LER and ~40% less LWR

Sub-10nm resolution



Resist features as narrow as ~8nm have been fabricated using PEC and multi-pass

Thank You!

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